

256K × 16 Bit CMOS Video RAM

FEATURES

- **Dual port Architecture**
256K × 16 bits RAM port
512 × 16 bits SAM port
- **Performance range:**

Parameter	Speed	-60	-70	-80
RAM access time (t _{RAC})		60ns	70ns	80ns
RAM access time (t _{CAC})		15ns	20ns	20ns
RAM cycle time (t _{RC})		110ns	130ns	150ns
RAM page cycle (t _{HPC})	KM4216C256	24ns	28ns	33ns
	KM4216V256	24ns	28ns	33ns
SAM access time (t _{SAC})		15ns	17ns	20ns
SAM cycle time (t _{SCC})		18ns	20ns	25ns
RAM active current	KM4216C256	120mA	110mA	100mA
	KM4216V256	110mA	100mA	90mA
SAM active current	KM4216C256	50mA	45mA	40mA
	KM4216V256	40mA	35mA	30mA

- **Fast Page Mode with Extended Data out**
- **RAM Read, Write, Read-Modify-Write**
- **Serial Read (SR)**
- **Read / Real time read transfer (RT, RRT)**
- **Split Read Transfer with Stop Operation (SRT)**
- **Byte/Word Write Operation**
- **8 Column Block Write (BW) and Write-per-Bit with Masking Operation (New and Old Mask)**
- **CAS-before-RAS, RAS-only and Hidden Refresh**
- **Common Data I/O Using three state RAM Output control**
- **All Inputs and Outputs TTL Compatible**
- **Refresh: 512 Cycle/8ms**
- **Single + 5V ± 10% Supply Voltage (KM4216C256)**
- **Single + 3.3V ± 10% Supply Voltage (KM4216V256)**
- **Plastic 64-Pin 525 mil SSOP (0.8mm pin pitch)**
- **Plastic 70-pin 400mil TSOP II (0.65mm pin pitch) (Forward and Reverse Type)**
- **Device Options**
 - Low Power Dissipation
 - Extended CBR Refresh (64ms) L
 - Low Low Power Dissipation Self Refresh (128ms) F
- **Low V_{CC}(3.3V) Part Name: KM4216V256**
- **Part Marking**

GENERAL DESCRIPTION

The Samsung KM4216C/V256 is a CMOS 256K × 16 bit Dual Port DRAM. It consists of a 256K × 16 dynamic random access memory (RAM) port and 512 × 16 static serial access memory (SAM) port. The RAM and SAM ports operate asynchronously except during data transfer between the ports.

The RAM array consists of 512 bit rows of 8192 bits. It operates like a conventional 256K × 16 CMOS DRAM. The RAM port has a write per bit mask capability. Data may be written with New and Old Mask. The RAM port has a Fast Page mode access with Extended Data out, Byte/word write operation and Block Write capabilities.

The SAM port consists of sixteen 512 bit high speed shift registers that are connected to the RAM array through a 8192 bit data transfer gate. The SAM port has serial read capability.

Data may be internally transferred from the RAM to SAM ports using read, and programmable (Stop Register) Split Transfers.

Refresh is accomplished by familiar DRAM refresh modes. The KM4216C/V256 supports RAS-only, Hidden, and CAS-before-RAS refresh for the RAM port. The SAM port does not require refresh.

All inputs and I/O's are TTL level compatible. All address lines and data inputs are latched on chip to simplify system design. The outputs are unlatched to allow greater system flexibility.

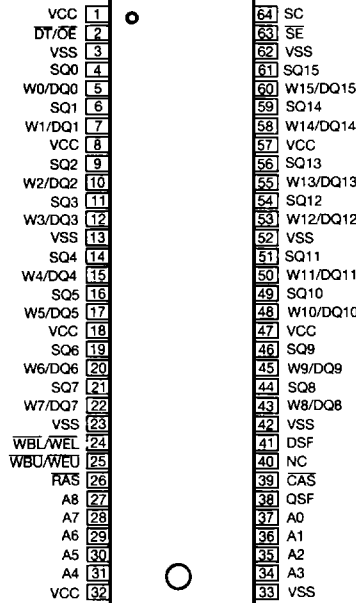
Pin Name	Pin Function	
SC	Serial Clock	
SQ ₀ -SQ ₁₅	Serial Data Output	
DT/OE	Data Transfer/Output Enable	
WBL/WEL, WBU/WEU	Write Per Bit/Write Enable (Lower /Upper)	
RAS	Row Address Strobe	
CAS	Column Address Strobe	
W ₀ /DQ ₀ -W ₁₅ /DQ ₁₅	Data Write Mask/Input/Output	
SE	Serial Enable	
A ₀ -A ₈	Address Inputs	
DSF	Special Function Control	
V _{CC}	KM4216C256	Power (+5V)
	KM4216V256	Power (+3.3V)
V _{SS}	Ground	
QSF	Special Flag Out	
N.C	No Connection	

KM4216C256/L/F, KM4216V256/L/F

PRELIMINARY CMOS VIDEO RAM

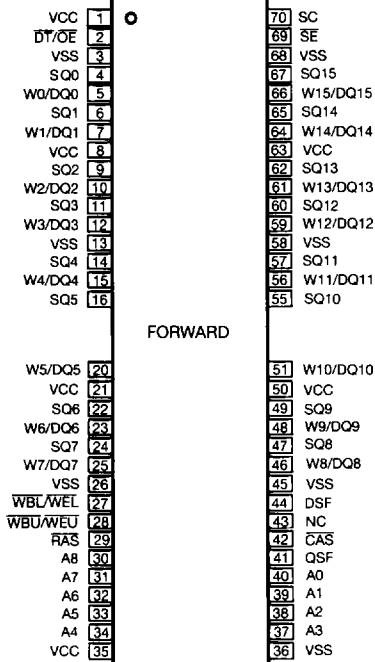
PIN CONFIGURATION (TOP VIEWS)

• KM4216C/V256G/GL/GF

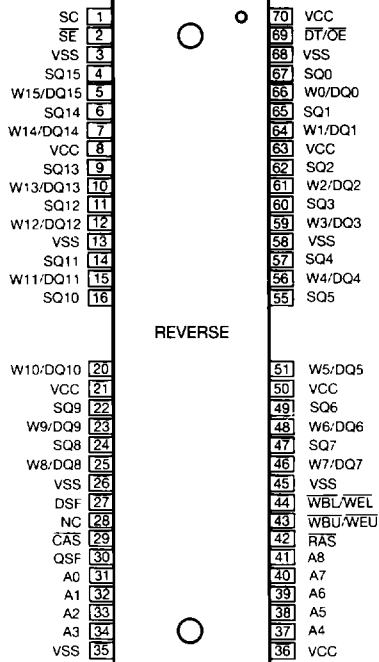


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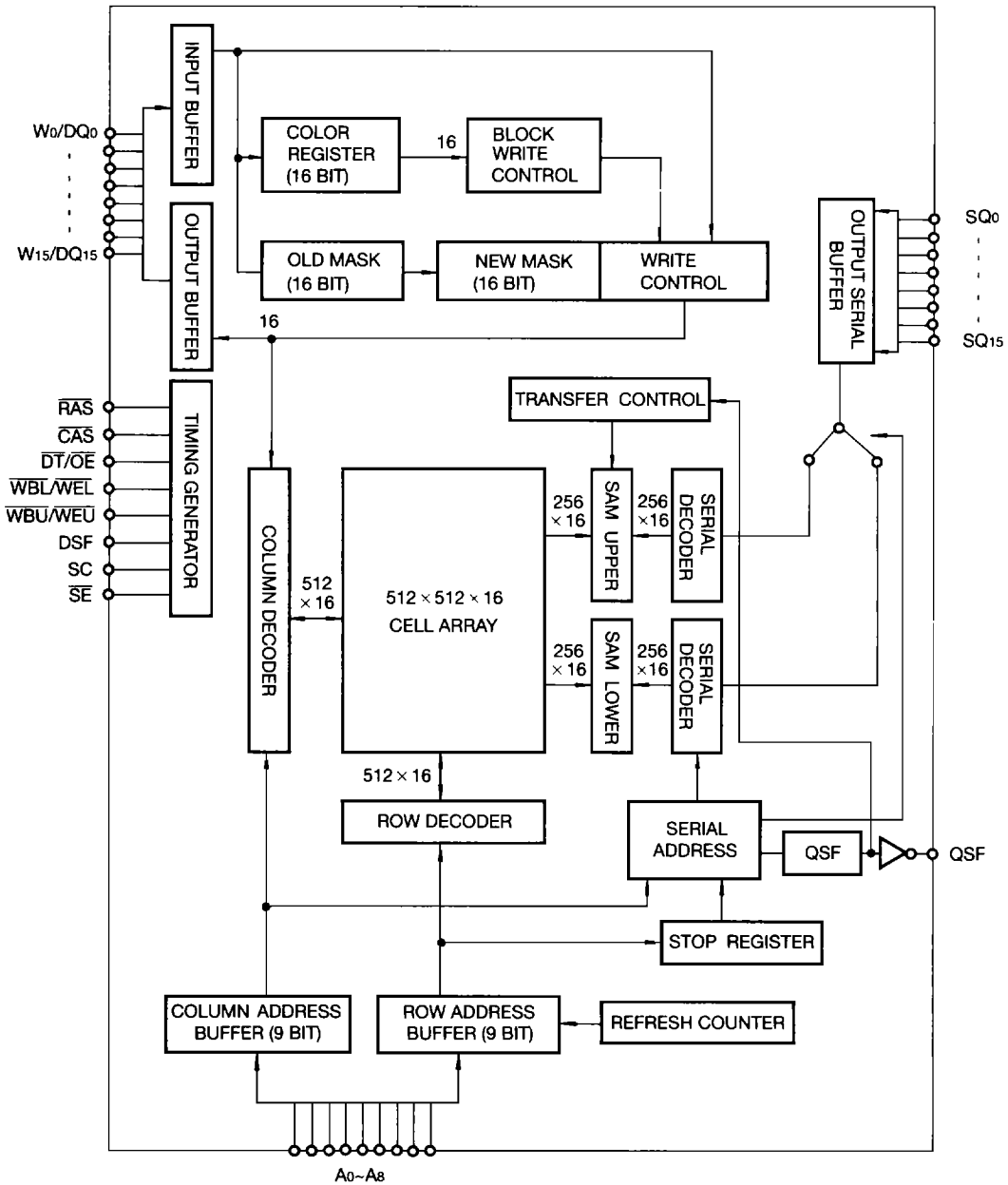
• KM4216C/V256T/TL/TF



• KM4216C/V256R/RL/RF



FUNCTIONAL BLOCK DIAGRAM



FUNCTION TRUTH TABLE

Mnemonic Code	RAS				CAS	Address		DQI Input		Register		Function
	CAS	DT/OE	WE	DSF	DSF	RAS	CAS	RAS	CAS/WE	Mask	Color	
CBRS (Note 1.3)	0	×	0	1	-	Stop (Note4)	-	×	-	-	-	CBR Refresh/ Stop (No reset)
CBRN (Note 1)	0	×	1	1	-	×	-	×	-	-	-	CBR Refresh (No reset)
CBRR (Note 1)	0	×	×	0	-	×	-	×	-	-	-	CBR Refresh (Option reset)
ROR	1	1	×	0	-	ROW	-	×	-	-	-	RAS-only Refresh
RT	1	0	1	0	×	ROW	Tap	×	×	-	-	Read Transfer
SRT	1	0	1	1	×	ROW	Tap	×	×	-	-	Split Read Transfer
RWM	1	1	0	0	0	ROW	Col.	WMi	Data	Use	-	Masked write (New/Old Mask)
BWM	1	1	0	0	1	ROW	Col.	WMi	Column Mask	Use	Use	Masked Block Write (New/Old Mask)
RW	1	1	1	0	0 (Note6)	ROW	Col.	×	Data	-	-	Read or Write
BW	1	1	1	0	1	ROW	Col.	×	Column Mask	-	Use	Block Write
LMR (Note 2)	1	1	1	1	0	ROW (Note7)	×	×	WMi	Load (Note5)	-	Load (Old) Mask Register set Cycle
LCR	1	1	1	1	1	ROW (Note7)	×	×	Color		Load	Load Color Register

X: Don't Care, - : Not Applicable, Tap: SAM Start (Column) Address, WMi : Write Mask Data (i=0-15)
RAS only refresh does not reset Stop or LMR functions.

Notes:

- (1) CBRS, CBRN and CBRR all perform $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycles. CBRR is used to reset all options and either CBRS or CBRN is used to continue to refresh the RAM without clearing any of the options.
- (2) After LMR cycle, RWM and BWM use old mask. (Use CBRR reset to new mask, use CBRS or CBRN to perform $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh while using Old mask)
- (3) After CBRS Cycle, SRT use STOP Register as a boundary address.
- (4) Stop defines the column on which shift out moves to the other half of the SAM.
- (5) After LMR, Mask Register is only changed by the another LMR or CBRR cycle.
- (6) In the case of read cycle, DSF is don't care
- (7) The ROW that is addressed will be refreshed, but a ROW address is not required.

ABSOLUTE MAXIMUM RATINGS*

Item	Symbol	Rating		Unit
		KM4216C256	KM4216V256	
Voltage on Any Pin Relative to Vss	V _{IN} , V _{OUT}	-1 to +7.0	-0.5 to V _{CC} +0.5	V
Voltage on Supply Relative to Vss	V _{CC}	-1 to +7.0	-0.5 to +4.6	V
Storage Temperature	T _{stg}	-55 to +150	55 to +150	°C
Power Dissipation	P _D	1	0.6	W
Short Circuit Output Current	I _{OS}	50	50	mA

* Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS (Voltage reference to Vss, T_A=0 to 70 °C)

Item	Symbol	KM4216C256			KM4216V256			Unit
		Min	Typ	Max	Min	Typ	Max	
Supply Voltage	V _{CC}	4.5	5.0	5.5	3.0	3.3	3.6	V
Ground	V _{SS}	0	0	0	0	0	0	V
Input High Voltage	V _{IH}	2.4	-	V _{CC} +1V	2.0	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL}	-1.0	-	0.8	-0.3	-	0.8	V

INPUT/OUTPUT CURRENT (Recommended operating conditions unless otherwise noted.)

Item	Symbol	Min	Max	Unit
Input Leakage Current (Any Input 0 ≤ V _{IN} ≤ V _{CC} +0.5(0.3*1) all other pins not under test=0 volts).	I _{IL}	-10	10	μA
Output Leakage Current (Data out is disabled, 0V ≤ V _{OUT} ≤ V _{CC})	I _{OL}	-10	10	μA
Output High Voltage Level (RAM I _{OH} =-2mA, SAM I _{OH} =-2mA)	V _{OH}	2.4	-	V
Output Low Voltage Level (RAM I _{OL} =2mA, SAM I _{OL} =2mA)	V _{OL}	-	0.4	V

Note) *1 : KM4216V256

CAPACITANCE (V_{CC}=5V, f=1MHz, T_A=25 °C)

Item	Symbol	Min	Max	Unit
Input Capacitance (A ₀ -A ₈)	C _{IN1}	2	6	pF
Input Capacitance (R _{AS} , C _{AS} , W _B /W _E , D _T /O _E , S _E , S _C , D _{SF})	C _{IN2}	2	7	pF
Input/Output Capacitance (W ₀ /DQ ₀ -W ₁₅ /DQ ₁₅)	C _{DQ}	2	7	pF
Output Capacitance (SQ ₀ -SQ ₁₅ , Q _{SF})	C _{SQ}	2	7	pF

DC AND OPERATING CHARACTERISTICS

(Recommended operating conditions unless other wise noted)

Parameter (RAM Port)	SAM port	Symbol	KM4216C256			KM4216V256			Unit
			-6	-7	-8	-6	-7	-8	
Operating Current*1 (\overline{RAS} and \overline{CAS} cycling @ $t_{RC}=\min$)	Standby*4	Icc1	120	110	100	110	100	90	mA
	Active	Icc1A	160	145	130	140	125	110	mA
Standby Current (\overline{RAS} , \overline{CAS} , $\overline{DT}/\overline{OE}$, $\overline{WB}/\overline{WE}=V_{IH}$ DSF= V_{IL})	Standby*4	Icc2	10	10	10	10	10	10	mA
	Active	Icc2A	50	45	40	40	35	30	mA
	Standby*4	Icc2C*2	200	200	200	200	200	200	μA
	Standby*4	Icc2C*3	150	150	150	150	150	150	μA
\overline{RAS} Only Refresh Current*1 ($\overline{CAS}=V_{IH}$, \overline{RAS} cycling @ $t_{RC}=\min$)	Standby*4	Icc3	120	110	100	110	100	90	mA
	Active	Icc3A	160	145	130	140	125	110	mA
Extended Fast Page Mode Current*1 ($\overline{RAS}=V_{IL}$, \overline{CAS} Cyclic @ $t_{PC}=\min$)	Standby*4	Icc4	110	100	90	100	90	80	mA
	Active	Icc4A	150	135	120	130	115	110	mA
\overline{CAS} Before- \overline{RAS} Refresh Current*1 (\overline{RAS} and \overline{CAS} Cycling @ $t_{RC}=\min$)	Standby*4	Icc5	120	110	100	110	100	90	mA
	Active	Icc5A	160	145	130	140	125	110	mA
Data Transfer Current *1 (\overline{RAS} and \overline{CAS} Cycling @ $t_{RC}=\min$)	Standby*4	Icc6	140	130	120	130	120	110	mA
	Active	Icc6A	180	165	150	160	145	130	mA
Block Write Cycle Current *1 (\overline{RAS} and \overline{CAS} Cycling @ $t_{RC}=\min$)	Standby*4	Icc7	120	110	100	110	100	90	mA
	Active	Icc7A	160	145	130	140	125	110	mA
Color Register Load Current *1 (\overline{RAS} and \overline{CAS} Cycling @ $t_{RC}=\min$)	Standby*4	Icc8	110	90	80	90	80	70	mA
	Active	Icc8A	140	125	110	120	105	90	mA
Battery Back Up Current *2 $\overline{CAS}=\overline{CAS}$ Before \overline{RAS} Refresh Cycling or $\leq V_{IL}$ $t_{RAS}=t_{RAS}(\min)$ to $1\mu s$ $t_{RC}=125\mu s$ (64ms for 512 rows) $\overline{DT}/\overline{OE}$, $\overline{WB}/\overline{WE}$, DSF $\geq V_{IH}$ or $\leq V_{IL}$	Standby*4	Icc9	300	300	300	300	300	300	μA
Self Refresh Current *3 $\overline{RAS}, \overline{CAS} \leq 0.2V$ (128ms for 512 rows) $\overline{DT}/\overline{OE}$, $\overline{WB}/\overline{WE}$, DSF $\geq V_{CC} - 0.2V$ or $\leq 0.2V$ DQ0~15= $V_{CC} - 0.2V$, 0.2V or OPEN	Standby*4	Icc10	250	250	250	250	250	250	μA

Note *1 Real values dependent on output loading and cycle rates. Specified values are obtained with the output open, Icc is specified as average current.

In Icc1, Icc3, Icc6, Icc7, Icc8, address transition should be changed only once while $\overline{RAS}=V_{IL}$.

In Icc4, Address transition should be changed only once while $\overline{CAS}=V_{IH}$

*2 KM4216C/V256L only : $V_{IH} \geq V_{CC} - 0.2V$, $V_{IL} \leq 0.2V$

*3 KM4216C256F only : $V_{IH} \geq V_{CC} - 0.2V$, $V_{IL} \leq 0.2V$

*4 SAM standby condition : $\overline{SE} \geq V_{IH}$, $SC \leq V_{IL}$ or $\geq V_{IH}$

AC CHARACTERISTICS (0°C ≤ T_A ≤ 70°C, KM4216C256 : V_{CC} = 5.0V ± 10%, KM4216V256 : 3.3V ± 10%.)

Parameter	Symbol	-6		-7		-8		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Random read or write cycle time	t _{RC}	110		130		150		ns	
Read-modify-write cycle time	t _{RWC}	155		185		200		ns	
Hyper page cycle time	t _{HPC}	30		35		40		ns	17
		24		28		33		ns	16
Hyper page read-modify-write cycle time	t _{HPRWC}	80		85		90		ns	
Access time from $\overline{\text{RAS}}$	t _{RAC}		60		70		80	ns	3,5,11
Access time from $\overline{\text{CAS}}$	t _{CAC}		15		20		20	ns	3,5,6
Access time from column address	t _{AA}		30		35		40	ns	3,11
Access time from $\overline{\text{CAS}}$ precharge	t _{CPA}		35		40		45	ns	3
$\overline{\text{CAS}}$ to output in Low-Z	t _{CLZ}	3		3		3		ns	3
Output buffer turn-off delay	t _{OFF}	0	15	0	15	0	15	ns	7
Transition time(rise and fall)	t _T	2	50	2	50	2	50	ns	2
$\overline{\text{RAS}}$ precharge time	t _{RP}	40		50		60		ns	
$\overline{\text{RAS}}$ pulse width	t _{RAS}	60	10K	70	10K	80	10K	ns	
$\overline{\text{RAS}}$ pulse width (Hyper page mode)	t _{RASP}	60	100K	70	100K	80	100K	ns	
$\overline{\text{RAS}}$ hold time	t _{RSH}	15		20		20		ns	
$\overline{\text{CAS}}$ hold time	t _{CSH}	45		55		65		ns	
$\overline{\text{CAS}}$ pulse width	t _{CAS}	15		15		20		ns	17
		10	10K	10	10K	12	10K	ns	16
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ delay time	t _{RCD}	20	45	20	50	20	60	ns	5
$\overline{\text{RAS}}$ to column address delay time	t _{RAD}	15	30	15	35	15	40	ns	11
$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ precharge time	t _{CRP}	5		5		5		ns	
$\overline{\text{CAS}}$ precharge time(C-B-R counter test cycle)	t _{CPT}	20		25		30		ns	
$\overline{\text{CAS}}$ precharge time (Hyper page mode)	t _{CP}	10		10		10		ns	
Output hold time from $\overline{\text{CAS}}$	t _{DOH}	5		5		5		ns	
Row address set-up time	t _{ASR}	0		0		0		ns	
Row address hold time	t _{RAH}	10		10		10		ns	
Column address set-up time	t _{ASC}	0		0		0		ns	
Column address hold time	t _{CAH}	10		12		15		ns	
Column address to $\overline{\text{RAS}}$ lead time	t _{RAL}	30		35		40		ns	
Read command set-up time	t _{RCS}	0		0		0		ns	
Read command hold referenced to $\overline{\text{CAS}}$	t _{RCH}	0		0		0		ns	9
Read command hold referenced to $\overline{\text{RAS}}$	t _{RRH}	0		0		0		ns	9
Output buffer turn off delay from $\overline{\text{WBX}}/\overline{\text{WEX}}$	t _{WEZ}	0	15	0	15	0	15	ns	7
Write command pulse width	t _{WPZ}	10		10		10		ns	7
Write command hold time	t _{WCH}	10		10		15		ns	
Write command pulse width	t _{WP}	10		10		15		ns	

AC CHARACTERISTICS (Continued)

Parameter	Symbol	-6		-7		-8		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Write command to \overline{RAS} lead time	trWL	15		15		20		ns	
Write command to \overline{CAS} lead time	tcWL	15		15		20		ns	
Data set-up time	tDS	0		0		0		ns	10
Data hold time	tDH	10		12		15		ns	10
Write command set-up time	twCS	0		0		0		ns	8
\overline{CAS} to \overline{WE} delay	tcWD	40		45		45		ns	8
\overline{RAS} to \overline{WE} delay	trWD	85		95		105		ns	8
Column address to \overline{WE} delay time	tAWD	50		55		60		ns	8
\overline{CAS} set-up time (\overline{C} - \overline{B} - \overline{R} refresh)	tCSR	10		10		10		ns	
\overline{CAS} hold time (\overline{C} - \overline{B} - \overline{R} refresh)	tCHR	10		10		10		ns	
\overline{RAS} precharge to \overline{CAS} hold time	trPC	10		10		10		ns	
\overline{RAS} hold time referenced to \overline{OE}	tROH	15		20		20		ns	
Access time from output enable	toEA		15		20		20	ns	
Output enable to data input delay	toED	15		15		15		ns	
Output Buffer turn-off delay from \overline{OE}	toEZ	0	15	0	15	0	15	ns	7
Output enable command hold time	toEH	15		15		15		ns	
Data to \overline{CAS} delay	tdZC	0		0		0		ns	
Data to output enable delay	tdZO	0		0		0		ns	
Refresh period (512 cycle)	tREF		8		8		8	ms	
\overline{WB} set-up time	tWSR	0		0		0		ns	
\overline{WB} hold time	trWH	10		10		15		ns	
DSF set-up time referenced to \overline{RAS}	tFSR	0		0		0		ns	
DSF hold time referenced to \overline{RAS}	trFH	10		10		15		ns	
DSF set-up time referenced to \overline{CAS}	tFSC	0		0		0		ns	
DSF hold time referenced to \overline{CAS}	trFH	10		15		15		ns	
Write per bit mask data set-up time	tMS	0		0		0		ns	
Write per bit mask data hold time	tMH	10		10		15		ns	
\overline{RAS} pulse width (\overline{C} - \overline{B} - \overline{R} self refresh)	trASS	100		100		100		μ s	15
\overline{RAS} precharge time (\overline{C} - \overline{B} - \overline{R} self refresh)	trPS	110		130		150		ns	15
\overline{CAS} hold time (\overline{C} - \overline{B} - \overline{R} self refresh)	tCHS	0		0		0		ns	15
\overline{DT} high set-up time	tTHS	0		0		0		ns	
\overline{DT} high hold time	tTHH	10		10		15		ns	
\overline{DT} low set-up time	tTLS	0		0		0		ns	
\overline{DT} low hold time	tTLH	10		10		15		ns	
\overline{DT} low hold referenced to \overline{RAS} (real time read transfer)	trTH	50		60		65		ns	
\overline{DT} low hold referenced to \overline{CAS} (real time read transfer)	tCTH	15		20		25		ns	

AC CHARACTERISTICS (Continued)

Parameter	Symbol	-6		-7		-8		Unit	Notes
		Min	Max	Min	Max	Min	Max		
\overline{DT} low hold referenced to column address (real time read transfer)	tATH	20		25		30		ns	
\overline{DT} precharge time	tTP	20		20		20		ns	
\overline{RAS} to first SC delay (read transfer)	tRSD	60		70		80		ns	
\overline{CAS} to first SC delay (read transfer)	tCSD	25		30		35		ns	
Col. Address to first SC delay (read transfer)	tASD	30		35		40		ns	
Last SC to \overline{DT} lead time	tTSL	5		5		5		ns	
\overline{DT} to first SC delay time (read transfer)	tTSD	10		10		15		ns	
LAST SC to \overline{RAS} set-up time	tSRS	20		20		20		ns	
SC cycle time	tSCC	18		20		25		ns	14
SC pulse width (SC high time)	tSC	5		7		7		ns	
SC precharge (SC low time)	tSCP	5		7		7		ns	
Access time from SC	tSCA		15		17		20	ns	4
Serial output hold time from SC	tSOH	5		5		5		ns	
Access time from \overline{SE}	tSEA		15		17		20	ns	4
\overline{SE} pulse width	tSE	20		20		25		ns	
\overline{SE} precharge time	tSEP	20		20		25		ns	
Serial output turn-off from \overline{SE}	tSEZ	0	15	0	15	0	15	ns	7
Split transfer set-up time	tSTS	20		25		25		ns	
Split transfer hold time	tSTH	20		25		25		ns	
SC-QSF delay time	tSQD		20		25		25	ns	
\overline{DT} -QSF delay time	tTQD		20		25		25	ns	
\overline{RAS} -QSF delay time	tRQD		70		75		80	ns	
\overline{CAS} -QSF delay time	tCQD		35		35		40	ns	
\overline{DT} to \overline{RAS} Precharge time	tTRP	40		50		60		ns	
\overline{OE} high pulse width	tOEP	10		10		10		ns	
\overline{OE} high hold time from \overline{CAS} high	tOEHC	10		10		10		ns	
\overline{OE} to \overline{CAS} high set-up time	tOCH	5		5		5		ns	

NOTES

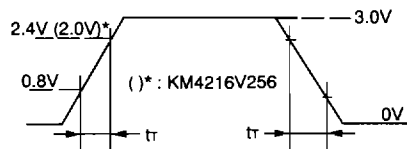
1. An initial pause of 200 μ s is required after power-up followed by any 8 \overline{RAS} , 8 SC cycles before proper device operation is achieved. ($\overline{DT}/\overline{OE}$ =High) if the internal refresh counter is used a minimum of 8 \overline{CAS} -before- \overline{RAS} initialization cycles are required in stead of 8 \overline{RAS} cycles.
2. $V_{IH}(\text{min})$ and $V_{IL}(\text{max})$ are reference levels for measuring timing of input signals. Transition times are measured between $V_{IH}(\text{min})$ and $V_{IL}(\text{max})$, and are assumed to be 5ns for all input signals. Input signal transition from 0V to 3V for AC timing.
3. RAM port outputs are measured with a load equivalent to 1TTL load and 50pF.
DOUT Comparator level : $V_{OH}/V_{OL}=2.0V/0.8V$.
4. SAM port outputs are measured with a load equivalent to 1TTL load and 30pF.
DOUT comparator level: $V_{OH}/V_{OL}=2.0/0.8V$.
5. Operation within the $t_{ACD}(\text{max})$ limit insures that $t_{RAC}(\text{max})$ can be met. The $t_{RCD}(\text{max})$ is specified as a reference point only. If t_{RCD} is greater than the specified $t_{RCD}(\text{max})$ limit, then access time is controlled exclusively by t_{CAC} .
6. Assumes that $t_{RCD} \geq t_{RCD}(\text{max})$.
7. This parameters define the time at which the output achieves the open circuit condition and are not referenced to V_{OH} or V_{OL} .
8. t_{WCS} , t_{RWD} , t_{CWD} and t_{AWD} are nonrestrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}(\text{min})$ the cycle is an early write cycle and the data out pin will remain high impedance for the duration of the cycle. If $t_{CWD} \geq t_{CWD}(\text{min})$ and $t_{RWD} \geq t_{RWD}(\text{min})$ and $t_{AWD} \geq t_{AWD}(\text{min})$, then the cycle is a read-write cycle and the data output will contain the data read from the selected address. If neither of the above conditions are satisfied, the condition of the data out is indeterminate.
9. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
10. These parameters are referenced to the \overline{CAS} leading edge in early write cycles and to the \overline{WE} leading edge in read-write cycles.
11. Operation within the $t_{RAD}(\text{max})$ limit insured that $t_{RAC}(\text{max})$ can be met. $t_{RAD}(\text{max})$ is specified as a reference point only. If t_{RAD} is greater than the

specified $t_{RAD}(\text{max})$ limit, then access time is controlled by t_{AA} .

12. Power must be applied to the \overline{RAS} and $\overline{DT}/\overline{OE}$ input signals to pull them high before or at the same time as the V_{CC} supply is turned on. After power-up, initial status of chip is described below

Pin or REGISTER	STATUS
QSF	Hi-Z
Color Register	Don't Care
Write Mask Register	Don't Care
Tap Pointer	Invalid
Stop Register	Default Case
Wi/DQi	Hi-Z
SAM Port	Hi-Z
SQi	Hi-Z

13. Recommended operating input condition.



Input pulse levels are from 0.0V to 3.0Volts. All timing measurements are referenced from $V_{IL}(\text{max})$ and $V_{IH}(\text{min})$ with transition time=5.0ns

14. Assume $t_r=3\text{ns}$.
15. Self refresh parameter (KM4216C/V256F) 512K cycle of burst refresh must be executed within 8ms before and after self-refresh in order to meet refresh specification.
16. $t_{ASC} \geq t_{CP}(\text{min})$ at normal cycle assume $t_r=2\text{ns}$.
17. $t_{ASC} < t_{CP}(\text{min})$ at normal cycle or any condition at Block write cycle assume $t_r=2\text{ns}$.

DEVICE OPERATION

The KM4216C/V256 contains 4,194,304 memory locations. Eighteen address bits are required to address a particular 16 bit word in the memory array. Since the KM4216C/V256 has only 9 address input pins, time multiplexed addressing is used to input 9 row and 9 column addresses. The multiplexing is controlled by the timing relationship between the row address strobe (\overline{RAS}), the column address strobe(\overline{CAS}) and the valid row and column address inputs.

Operation of the KM4216C/V256 begins by strobing in a valid row address with \overline{RAS} while \overline{CAS} remains high. Then the address on the 9 address input pins are changed from a row address to a column address and are strobed in by \overline{CAS} . This the beginning of any KM4216C/V256 cycle in which a memory location is accessed. The specific type of cycle is determined by the state of the write enable pin and various timing relationship. The cycle is terminated when both \overline{RAS} and \overline{CAS} have returned to the high state. Another cycle can be initiated after \overline{RAS} remains high long enough to satisfy the \overline{RAS} precharge time (t_{RP}) requirement.

\overline{RAS} and \overline{CAS} Timing

The minimum \overline{RAS} and \overline{CAS} pulse widths are specified by $t_{RAS(min)}$ and $t_{CAS(min)}$ respectively. These minimum pulse widths must be satisfied for proper device operation and data integrity. Once a cycle is initiated by bringing \overline{RAS} low, it must not be aborted prior to satisfying the minimum \overline{RAS} and \overline{CAS} pulse widths. In addition, a new cycle must not begin until the minimum \overline{RAS} precharge time, t_{RP} , has been satisfied. Once a cycle begins, internal clocks and other circuits within the KM4216C/V256 begin a complex sequence of events. If the sequence is broken by violating minimum timing requirement, loss of data integrity can occur.

RAM Read

A RAM read cycle is achieved by maintaining $\overline{WB}/\overline{WE}$ high during a $\overline{RAS}, \overline{CAS}$ cycle. The access time is normally specified with respect to the falling edge of \overline{RAS} . But the access time also depends on the falling edge of \overline{CAS} and on the valid column address transition.

If \overline{CAS} goes low before $t_{RCD(max)}$ and if the column address is valid before $t_{RAD(max)}$ then the access time to valid data is specified by t_{RAC} . However, if \overline{CAS} goes low after $t_{RCD(max)}$ or the column address becomes valid after $t_{RAD(max)}$, access is specified by t_{CAC} or t_{AA} . The KM4216C/V256 has common data I/O pins. The $\overline{DT}/\overline{OE}$ has been provided so the output buffer can be precisely controlled. For data to appear at the outputs, $\overline{DT}/\overline{OE}$ must be low for the period of time defined by t_{OEA} .

Extended Data Out

In the conventional RAM Read cycle, $Dout$ buffer is designed to make turn-off by the rising edge of \overline{CAS} . The KM4216C/V256 offers an accelerated Fast Page Mode Cycle by eliminating output disable from \overline{CAS} high.

This is called Extended Data Output (or Hyper Page mode)

Data output are disabled at $\overline{WB}/\overline{WE}=low, \overline{DT}/\overline{OE}=high$ and t_{OFF} time after \overline{RAS} and \overline{CAS} are high. The t_{OFF} time is referenced from the rising edge of \overline{RAS} or \overline{CAS} , whichever occurs later (See Figure 1). What the output buffer is disabling during $\overline{DT}/\overline{OE} = high$ is to use bank selection in the frame buffer memory using common I/O line. Read, write and read-modify-write cycles are available during the extended data out mode.

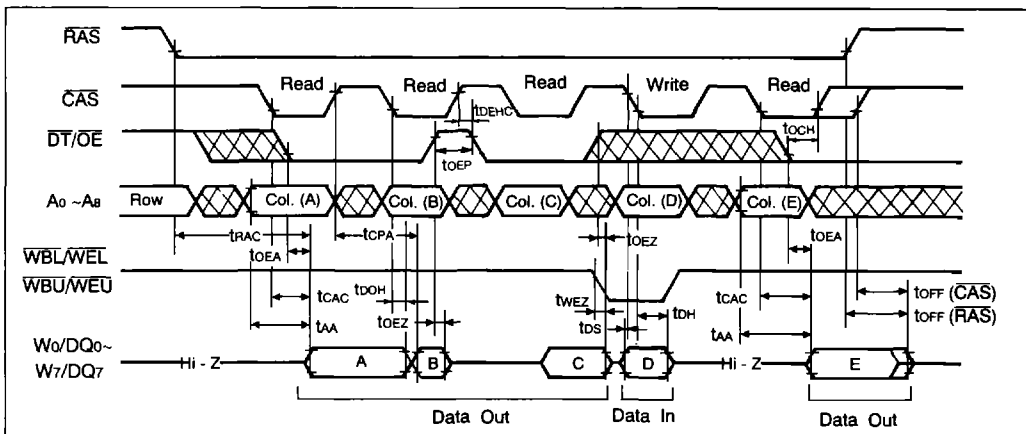


Figure 1. Extended Data Output Example

DEVICE OPERATION (continued)

Byte Write Operation

The KM4216C/V256 has 2 write control pin, $\overline{WBL}/\overline{WEL}$ and $\overline{WBU}/\overline{WEU}$, and offers asynchronous write operation with lower byte ($W_0/DQ_0-W_7/DQ_7$) and upper byte ($W_8/DQ_8-W_{15}/DQ_{15}$). This is called Byte Write operation. This operation can be performed in RAM write, Block write, Load Mask register, and Load Color register.

New Masked Write Per Bit

The New Masked Write Per Bit cycle is achieved by maintaining \overline{CAS} high and $\overline{WB}/\overline{WE}$ and \overline{DSF} low at the falling edge of \overline{RAS} . The mask data on the $W_0/DQ_0-W_{15}/DQ_{15}$ pins are latched into the write mask register at the falling edge of \overline{RAS} . When the mask data is low, writing is inhibited into the RAM and the mask data is high, data is written into the RAM.

The mask data is valid for only one cycle. Mask data must be provided in every write cycle that a masking operation is desired.

The Early Write cycle is achieved by $\overline{WB}/\overline{WE}$ low before \overline{CAS} falling and the Late Write cycle is achieved by $\overline{WB}/\overline{WE}$ low after \overline{CAS} falling. During the Early or Late Write cycle, input data through $W_0/DQ_0-W_{15}/DQ_{15}$ must keep the set-up and hold time at the falling edge of \overline{CAS} or $\overline{WB}/\overline{WE}$.

If $\overline{WBL}/\overline{WEL}$ and $\overline{WBU}/\overline{WEU}$ is high at the falling edge of \overline{RAS} , no masking operation is performed (see Figure2, 3). And If $\overline{WBL}/\overline{WEL}$ is high during \overline{CAS} low, write operation of lower byte do not perform and if $\overline{WBU}/\overline{WEU}$ is high, write operation of upper byte do not execute.

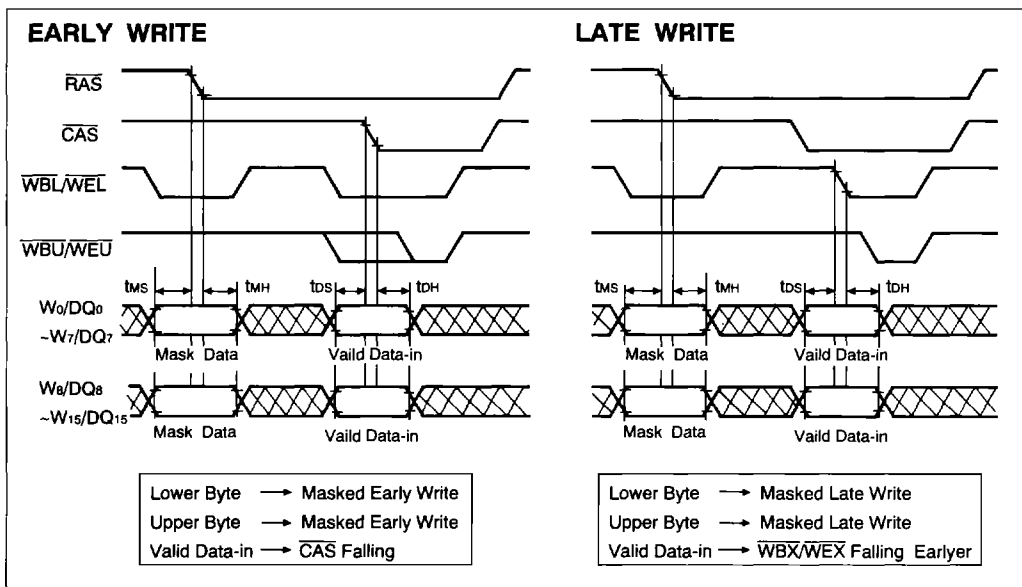


Figure 2. Byte Write and New Masked Write Cycle Example 1. (Early Write & Late Write)

DEVICE OPERATION (continued)

Load Mask Register(LMR)

The Load Mask Register operation loads the data present on the W_i/DQ_i pins into the Mask Data Register at the falling edge of CAS or WB/WE .

The LMR cycle is performed if DSF high, $\overline{WB/WE}$ high at the RAS falling edge and DSF low at the CAS falling edge. If an LMR is done, the KM4216C/V256 are set to old masked write mode.

Old Masked Write Per Bit

This mode is enabled through the Load Mask Register (LMR) cycle. If an LMR is done, all Masked write are Old

Masked Write Per Bit and the I/O mask data will be provided by the Mask Data Register (See Figure 4.)

The mask data is applied in the same manner as in New Masked write Per Bit mode.

Mask Data Register's content is changed by the another LMR. To reset the device back to the New Masked write mode, $CBRR$ (CBR refresh with option reset) cycle must be performed. After power-up, the KM4216C/V256 initializes in the New Masked write mode.

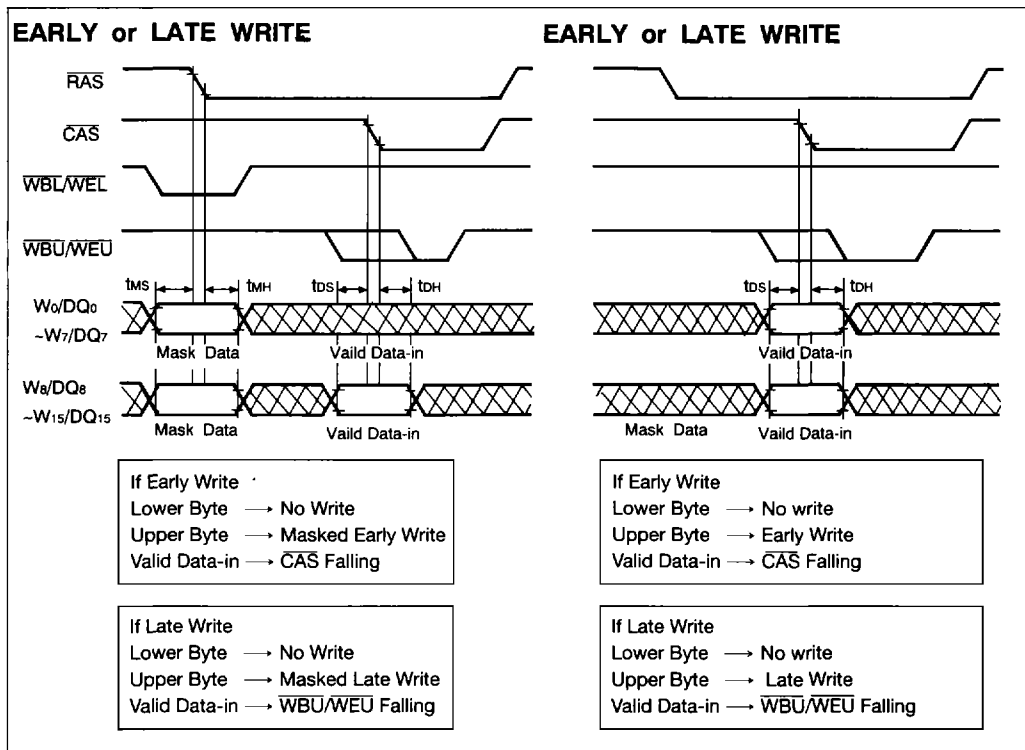


Figure 3. Byte Write and New Masked Write Cycle Example 2.

DEVICE OPERATION (continued)

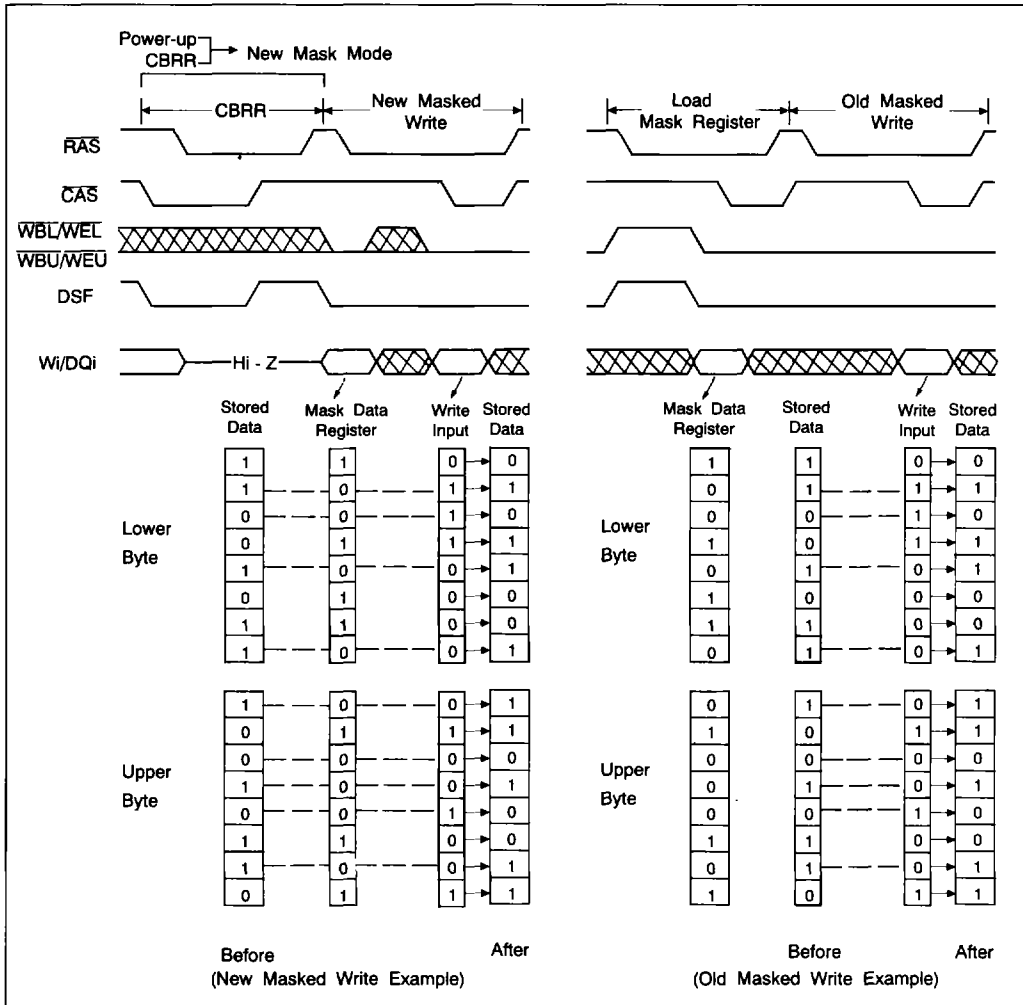


Figure 4. New Masked Write Cycle and Old Masked Write Cycle Example

Fast Page Mode

The KM4216C/V256 has Fast Page mode capability provides high speed read, write or read-modify-write access to all memory locations within a selected row. In this cycle, read, write, read-modify write, and block write cycles can be mixed in any order. In one RAS cycle, 512 word memory cells of the

same row address can be accessed. While RAS is held low to maintain the row address, CAS is cycled to strobe in additional column addresses. This eliminates the time required to set up and strobe sequential row addresses for the same page.

DEVICE OPERATION (continued)

Load Color Register(LCR)

A Load Color register cycle is performed by keeping DSF high on the both falling edges of \overline{RAS} and \overline{CAS} . Color data is loaded in the falling edge of \overline{CAS} (early write) or \overline{WE} (late write) via the $W_0/DQ_0-W_7/DQ_7$ (Lower Byte), $W_8/DQ_8-W_{15}/DQ_{15}$ (Upper Byte) pins. This data is used in Block Write cycles and remains unchanged until the next Load Color Register Cycle.

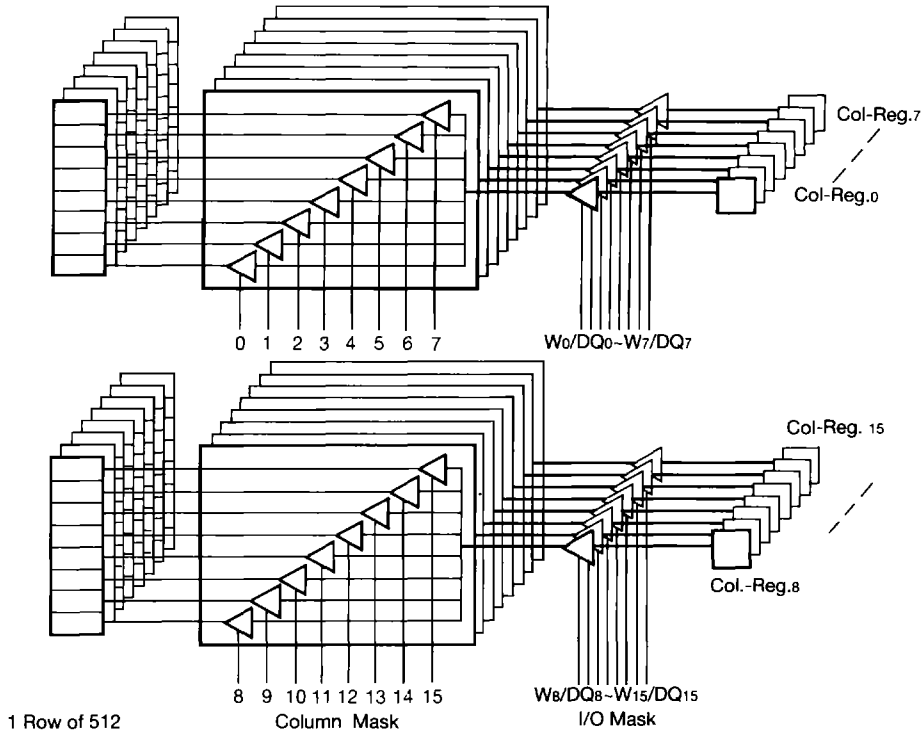
Block Write

In a Block write cycle 8 adjacent column locations can be written simultaneously with the same data, resulting

be written simultaneously with the same data, resulting in fast screen fills of the same color.

First, the internal 16-bit Color Register must be loaded with the data to be written by performing a Load Color Register(LCR) cycle. When a Block Write cycle is performed, each bit of the Color Register is written into 8 adjacent locations of the same row of each corresponding bit plane(16). This result in a total of 128-bits being written in a single Block write cycle compared to 16-bits in a normal write cycle.

The Block write cycle is performed if DSF is low at the falling edge of \overline{RAS} and high at the falling edge of \overline{CAS} .



1 Row of 512

	\overline{RAS}
W_0/DQ_0-7	Lower Block I/O Mask
W_8/DQ_8-15	Upper Block I/O Mask

	\overline{CAS}
A_0-A_2	Don't Care
W_0/DQ_0-7	Lower Block Column Select
W_8/DQ_8-15	Upper Block Column Select

A_2-A_0	Lower	Upper	Column Mask	
0 0 0	W_0/DQ_0	W_8/DQ_8	DQi=1	Column Enable
0 0 1	W_1/DQ_1	W_9/DQ_9		
0 1 0	W_2/DQ_2	W_{10}/DQ_{10}		
0 1 1	W_3/DQ_3	W_{11}/DQ_{11}		
1 0 0	W_4/DQ_4	W_{12}/DQ_{12}	DQi=0	Column Disable
1 0 1	W_5/DQ_5	W_{13}/DQ_{13}		
1 1 0	W_6/DQ_6	W_{14}/DQ_{14}		
1 1 1	W_7/DQ_7	W_{15}/DQ_{15}		

Figure 5. Block Write Scheme

DEVICE OPERATION (continued)

Address Lines: The row address is latched on the falling edge of \overline{RAS} .

Since 8 columns are being written at a time, the minimum increment required for the column address is latched on the falling edge of \overline{CAS} , the 3 LSBs, A_0 , A_1 , and A_2 are ignored and only bits (A_3 - A_8) are used to define the location of the first bit out of the eight to be written.

Data Lines: On the falling edge of \overline{CAS} , the data on the W_0/DQ_0 - W_{15}/DQ_{15} pins provide column mask data. That is, for each of the eight bits in all 16 -bits-planes, writing of Color Register contents can be inhibited. For example, if $W_0/DQ_0=1$ and $W_1/DQ_1=0$, then the Color Register contents will be written into the first bit out of the eight, but the second remains

unchanged. Fig. 5 shows the correspondence of each data line to the column mask bits.

A Masked Block Write cycle is identical to a New/old Masked Write-Per-bit cycle except that each of the 16-bit planes being masked is operating on 8 column locations instead of one.

To perform a Masked Block Write cycle, both DSF and $\overline{WB}/\overline{WE}$ must be low at the falling edge of \overline{RAS} . DSF must be high on the falling edge of \overline{CAS} . In new mask mode, Mask data is latched into the device via the W_0/DQ_0 - W_{15}/DQ_{15} pins on the falling edge of \overline{RAS} and needs to be re-entered for every new \overline{RAS} cycle. In old mask mode, I/O mask data will be provided by the Mask Data Register.

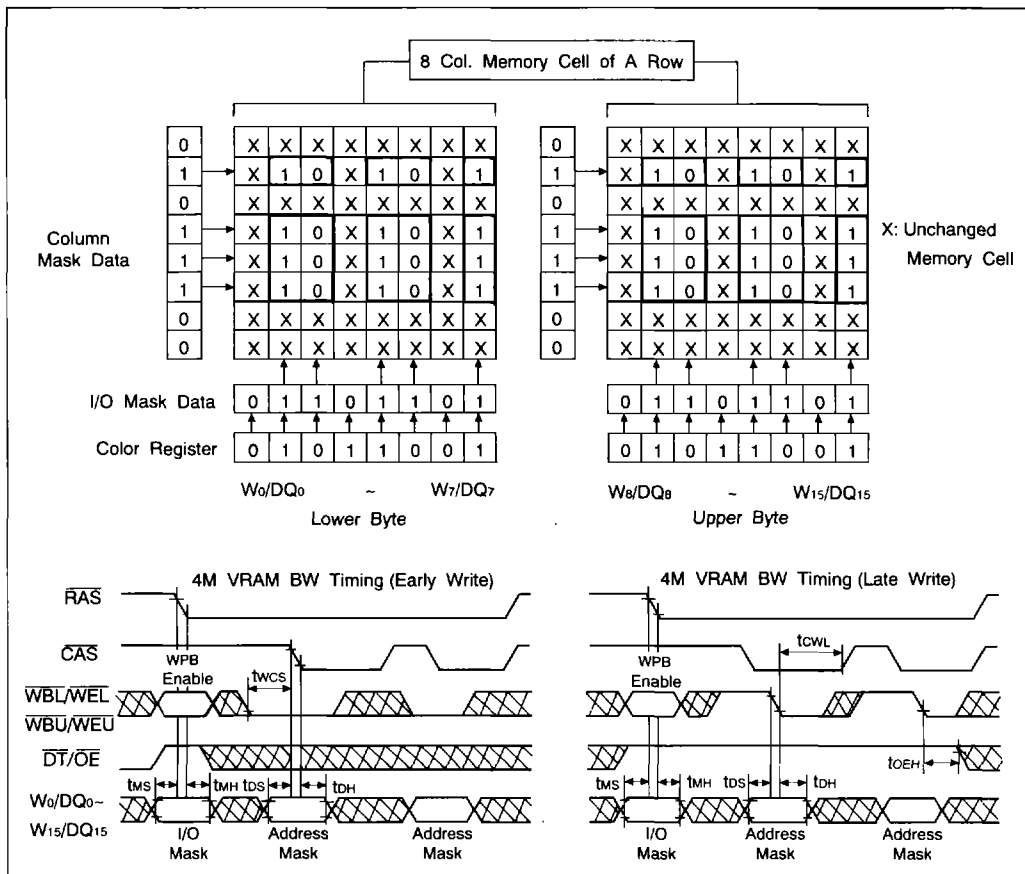


Figure 6. Block Write Example and Timing

DEVICE OPERATIONS (Continued)**Data Output**

The KM4216C/V256 has three state output buffer Controlled by $\overline{DT}/\overline{OE}$ and $\overline{CAS}/\overline{RAS}$. If $\overline{DT}/\overline{OE}$ is high when \overline{CAS} and \overline{RAS} low, the output state is in high impedance (High-z). In any cycle, the output goes low impedance state after tCLZ of the first \overline{CAS} falling edge. Invalid data may be present at the output during the time after tCLZ and the valid data appears at the output. The timing parameter tRAC, tCAC and tAA specify when the valid data will be present at the output.

Refresh

The data in the KM4216C/V256 is stored on a tiny capacitor within each memory cell. Due to leakage the data may leak off after a period of time. To maintain data integrity it is necessary to refresh each of the 512 rows every 8 ms. Any operation cycle performed in the RAM refreshes the 8192 bits selected by the row addresses or an on-chip refresh address counter. Either a burst refresh or distributed refresh may be used. There are several ways to accomplish this.

RAS-Only Refresh: This is the most common method for performing refresh. It is performed by strobing in a row address with \overline{RAS} while \overline{CAS} remains high. This cycle must be repeated for each of the 512 row address(A0-A8).

CAS-Before-RAS Refresh: The KM4216C/V256 has \overline{CAS} -before- \overline{RAS} on chip refresh capability that eliminates the need for external refresh addresses. If \overline{CAS} is held low for the specified set up time (tCSR) before \overline{RAS} goes low, the on chip refresh circuitry is enabled.

An internal refresh operation occurs automatically. The refresh address is supplied by the on chip refresh address counter which is then internally incremented in preparation for the next \overline{CAS} -before- \overline{RAS} refresh cycle.

The KM4216C/V256 has 3 type \overline{CAS} -before- \overline{RAS} refresh operation ; CBRR, CBRN, CBRS

CBRR (CBR Refresh with option reset) is set if DSF low at the \overline{RAS} falling edge. This mode initiates to change from old masked write to new masked write cycle, and reset stop register to default values

CBRN (CBR refresh without reset) is set if DSF high when $\overline{WBL}/\overline{WEL}$ and $\overline{WBU}/\overline{WEU}$ is high at the falling edge of \overline{RAS} and simply do only refresh operation.

CBRS(CBR Refresh with stop register set) cycle is set if DSF high when $\overline{WBL}/\overline{WEL}$ or $\overline{WBU}/\overline{WEU}$ is low and this mode is to set stop register's value.

Hidden Refresh: A hidden refresh cycle may be performed while maintaining the latest valid data at the output by extending the \overline{CAS} active time and cycling \overline{RAS} . The KM4216C/V256 hidden refresh cycle is actually a \overline{CAS} -before- \overline{RAS} refresh cycle within an extended read cycle. The refresh row address is the provided by the on-chip refresh address counter.

Self Refresh (Only KM4216C/V256F): The Self Refresh is \overline{CAS} -before- \overline{RAS} refresh to be used for longer periods of standby, such as a battery back-up. The initialization cycle of Self Refresh can be used by cycle named CBRN, CBRR, CBRS, If \overline{RAS} is low more than 100 μ s at the condition of CBR, Self Refresh function is accomplished. In this state, the external refresh address do not need to supply additionally on chip because the refresh counter on chip gives that addresses needed to refresh. Please note that the ending point of Self Refresh is when \overline{RAS} and \overline{CAS} is high and tRPS of Self Refresh is the time requiring to complete the last refresh of Self Refresh.

Other Refresh Methods : It is also possible to refresh the KM4216C/V256 by using read, write or read-modify-write cycles. Whenever a row is accessed, all the cells in that row are automatically refreshed. There are certain applications in which it might be advantageous to perform refresh in this manner but in general \overline{RAS} -only or \overline{CAS} -before- \overline{RAS} refresh is the preferred method.

DEVICE OPERATIONS (Continued)

Table 1. Truth Table for Transfer Operation

*: Don't care

RAS Falling Edg					Function	Transfer Direction	Transfer Data Bit
CAS	DT/OE	WB/WE	DSF	SE			
H	L	H	L	*	Read Transfer	RAM→SAM	512 × 16
H	L	H	H	*	Split Read Transfer	RAM→SAM	256 × 16

Transfer Operation

Transfer operation is initiated when $\overline{DT/OE}$ is low at the falling edge of \overline{RAS} . The state of DSF when \overline{RAS} goes low is used to select between normal transfer and split transfer cycle. Each of the transfer cycle is described in the truth table for transfer operation. (Table 1).

Read Transfer (RT)

The Read Transfer operation is set if $\overline{DT/OE}$ is low, $\overline{WB/WE}$ is high, and DSF is low, at the falling edge of \overline{RAS} . The row address bits in the read transfer cycle indicate which sixteen 512 bit DRAM row portions are transferred to the sixteen SAM data register portions. The column address bits indicate the start address of the SAM Registers when SAM data read operation is performed. If MSB of column address is low during Read transfer operation, the QSF state will be set low level and this indicates the start address of SAM register is present at lower half of SAM port. (If A8 is high, QSF will be high and means the start address is in upper half). Read Transfer may be accomplished in two ways. If the transfer is to be synchronized with the SC, $\overline{DT/OE}$ is taken high after \overline{CAS} goes low. This is usually called "Real Time Read Transfer". Note that the rising edge of $\overline{DT/OE}$ must be Synchronized with the rising edge of SC (trsl/trsd) to retain the continuity of serial read data output. If the transfer does not have to be synchronized with SC, $\overline{DT/OE}$ may go high before \overline{CAS} goes low and the actual data transfer will be timed internally.

Split Read Transfer (SRT)

In a graphic system, if data has to be transferred from DRAM to SAM while in the middle of a display line, the only way to do this seamlessly is by performing a Real Time Read Transfer cycle. However, this cycle has many critical timing restrictions (between SC, $\overline{DT/OE}$, \overline{RAS} and \overline{CAS}) because the transfer has to occur at the first rising edge of $\overline{DT/OE}$.

The Split Read Transfer cycle eliminates the need for this critical transfer timing, thereby simplifying system design. This is accomplished by dividing the SAM port into 2 halves of 256 bits each. A Split Read Transfer loads only the lower or upper half. While data is being serially read from one half of the SAM register, new RAM data can be transferred to the other half. Since transfer timing is controlled internally, there is no timing restriction between $\overline{DT/OE}$ and \overline{RAS} , \overline{CAS} , SC.

A normal Read Transfer cycle must be executed before performing a Split Read Transfer to set the state of QSF. A Split Read Transfer cycle is initiated by keeping DSF and $\overline{WB/WE}$ high and $\overline{DT/OE}$ low at the falling edge of \overline{RAS} .

DEVICE OPERATIONS (Continued)

Address: The row address is latched in the falling edge of \overline{RAS} . The column address defined by (A_0-A_7) defines the starting address of the SAM port from which data will begin shifting out. Column address pin A_8 is a "Don't care".

The QSF pin indicates which SAM half is shifting out serial data (0=Lower, 1=Upper). A split Read Transfer will load data into the other half. The state of the QSF output changes when the SAM address counter reaches a split SAM boundary (e.g.255th or 511th bit).

Example of SRT applications are shown in Fig.7 through Fig. 10

The normal usage of Split Read Transfer cycle is described in Fig.7. When Read Transfer is executed, data from X_1 row address is fully transferred to the SAM port and Serial Read is started from 0 (Tap

address). If SRT is performed while data is being serially read from lower half SAM, data from X_2 row address is transferred to upper half SAM. The Tap address of SRT is loaded after the boundary location of lower half SAM(255th SC) is accessed and the QSF state is changed into high level at the rising edge of 255th SC. Note that in this case "256+ Y_0 " Tap address instead of " Y_0 " is loaded.

The another example of SRT cycle is described in Fig.8 When Serial Read is performed after executing RT and SRT in succession, the data accessed by first SC is the data of RT Tap address. Serial data access from the starting address given by SRT cycle is performed after the data of RT to lower boundary (255th SC) is completed. Fig. 9 and 10 are the example of abnormal SRT cycle.

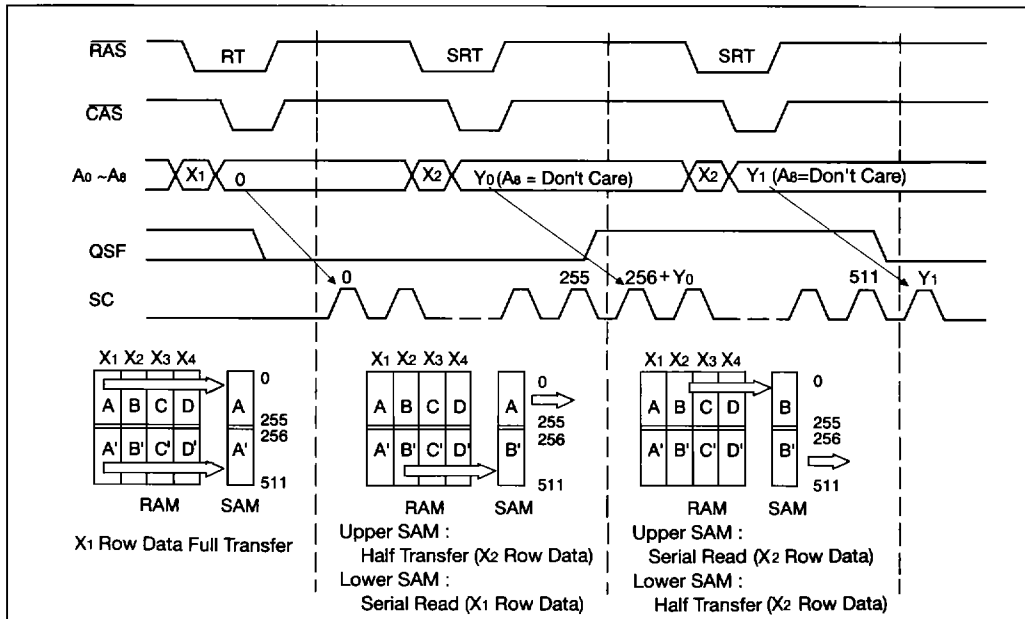


Figure 7. Split Read Transfer Normal Usage (Case1)

DEVICE OPERATIONS (Continued)

If SRT1 and SRT2 are performed in succession before accessing the boundary like Fig.9, the data transferred by SRT2 overwrite the data transferred by SRT1, so that data followed by SRT2 will be remain in the upper half SAM. The Serial Read after lower boundary 255th SC is started from the starting address given by SRT2 cycle. The Fig. 10 indicates that SRT cycle is not performed until Serial Read is completed to the boundary

511, therefore accessed data from 0 address corresponds to the old data transferred by RT. Note that there is not allowed period of SRT cycle. Since a SRT cycle must be ended before t_{STH} and started after t_{STS} , a split transfer is not allowed during $t_{STH} + t_{STS}$ (See Figure 11.)

A split Read Transfer does not change the direction of the SAM I/O port.

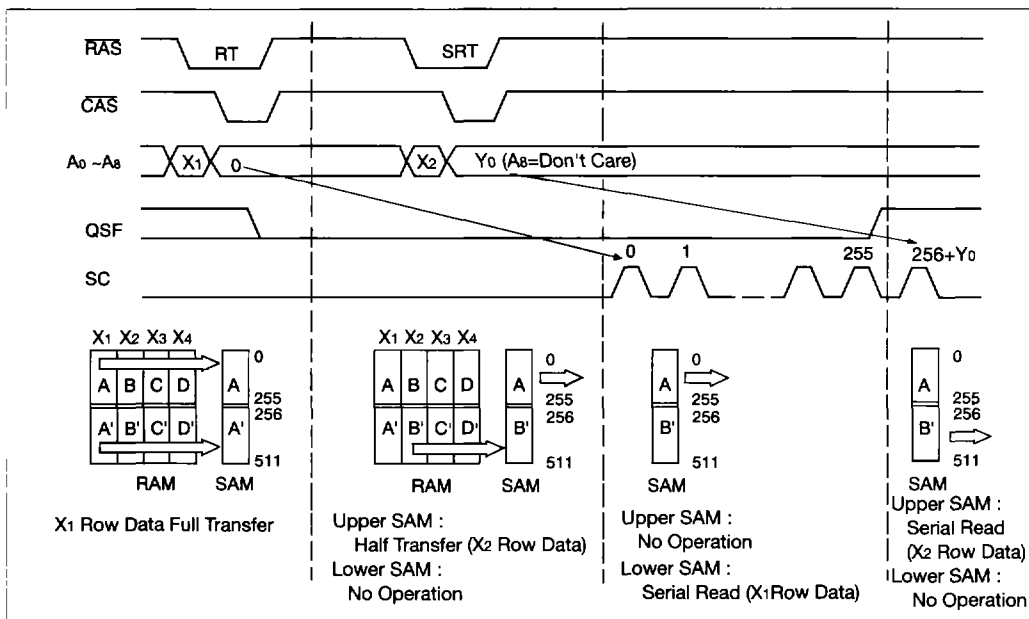


Figure 8. Split Read Transfer Normal Usage (Case 2)

DEVICE OPERATION (Continued)

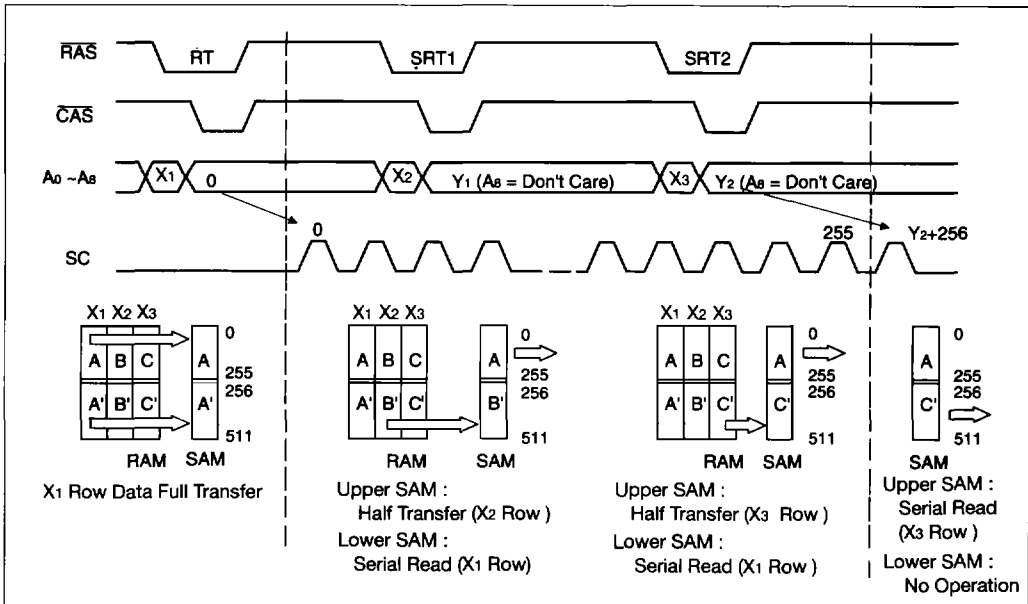


Figure 9. Split Read Transfer Abnormal Usage (Case 1)

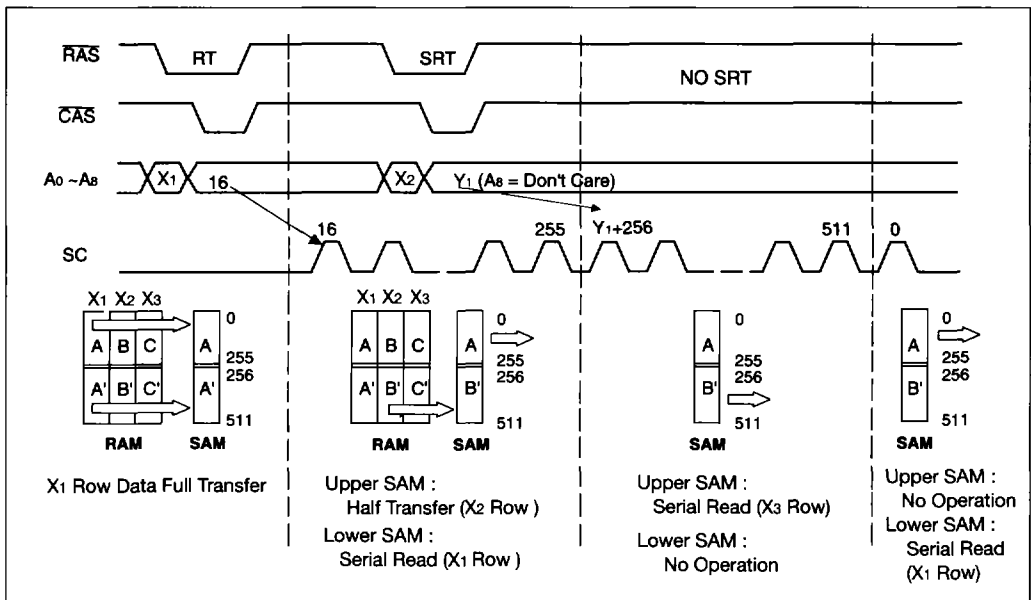


Figure 10. Split Read Transfer Abnormal Usage (Case 2)

DEVICE OPERATION (Continued)

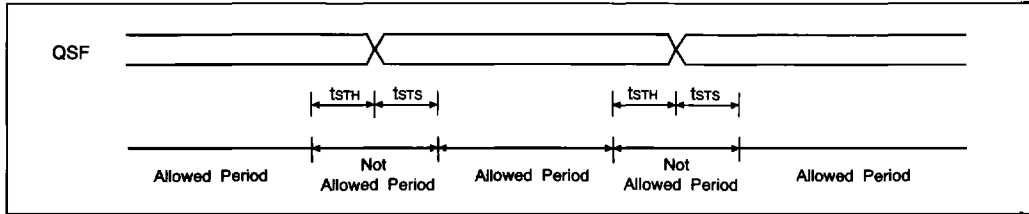


Figure 11. Split Transfer Cycle Limitation Period

Programmable Split SAM

In split SAM mode, SAM is divided into the lower half and the upper half.

After the last address of each half SAM(255 or 511) is accessed, the access will be changed one half of the SAM to the other half (at the loaded TAP address).

This last address is called Stop Point.

The KM4216C/V256 offers user-programmable Stop Point. The Stop Points and size of the resulting partitions are shown in Table 2. The Stop Points are set by performing CBRS cycle. The CBRS cycle's condition is $\overline{WBL}/\overline{WEL}$ or $\overline{WBU}/\overline{WEU}$ low, DSF high at the falling edge of \overline{RAS} in CBR cycle and the Stop Point is determined by row address entering at this time.

The Stop Point will not become valid until a SRT cycle is done. The Stop Point do not effect to SAM in normal RT, RRT cycle.

In Figure 12. programmable split SAM operation is shown. If a SRT cycle was done before the partition boundary (383), the access will jump to the TAP address(70) of the next half. Otherwise, the access will continue in the same half until a SRT occurs or the SAM half boundary (255, 511).

Note that the Stop Point may be changed at any time by performing another CBRS, and new Stop Point will

not be valid until a SRT is performed. To reset Stop Point, CBRR cycle must be performed. CBRR is a CBR cycle with DSF low at the falling edge of \overline{RAS} . The CBRR will take effect immediately; it does not require a SRT to become active valid.

Table 2. Stop Point Setting Address

Stop Register= Store Address of Serial Access							
Use on the Split Transfer Cycle							
Stop Pointer Set → CBRS Cycle							
Number of stop Points/Half	Partition	Stop Point Setting Address					
		A8	A7	A6	A5	A4	A3-A0
1	$(1 \times 256) \times 2$	x	1	1	1	1	x
2	$(2 \times 128) \times 2$	x	0	1	1	1	x
4	$(4 \times 64) \times 2$	x	0	0	1	1	x
8	$(8 \times 32) \times 2$	x	0	0	0	1	x
16	$(16 \times 16) \times 2$	x	0	0	0	0	x

*Other Case=Inhibit
X=Don't Care

DEVICE OPERATION (Continued)

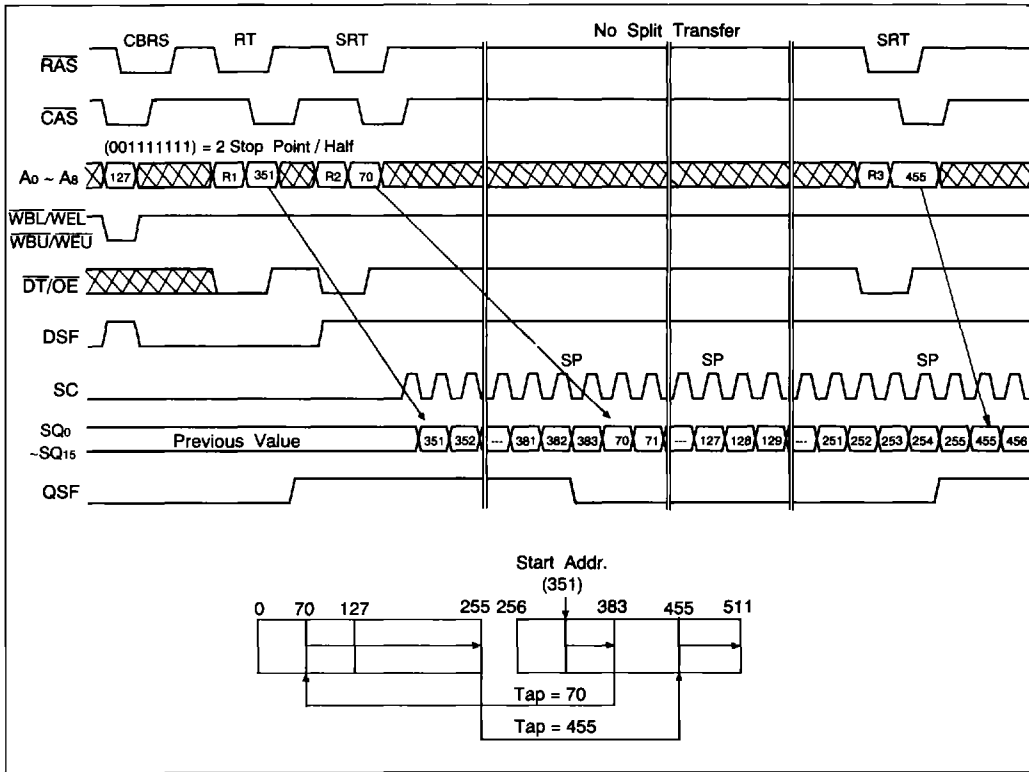
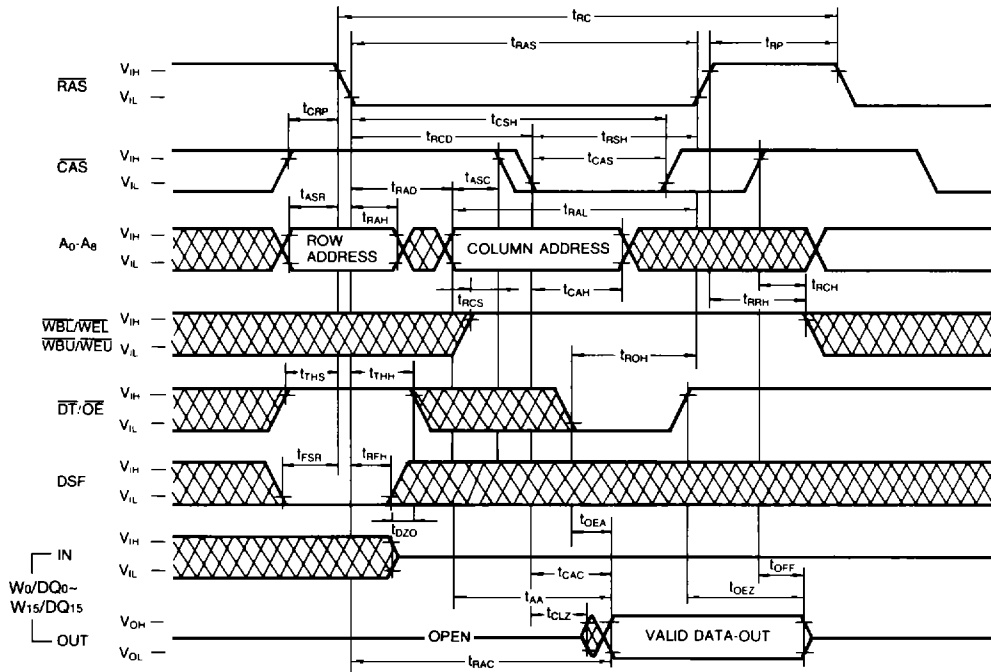


Figure 12. Programmable Split SAM operation

TIMING DIAGRAMS

READ CYCLE



 Don't Care

Truth Table for Write Cycle(1)

FUNCTION	RAS			CAS	CAS or WBL(U)/WEL(U)
	*1 WBL/WEL (WBU/WEU)	*2 DSF	*3 Wi/DQi (3) (New Mask)	*4 DSF	*5 Wi/DQi
Normal write	1	0	×	0	Write Data
Masked Write	0	0	Write Mask	0	Masked Write Data
Block Write (No I/O Mask) (4)	1	0	×	1	Column Mask
Masked Block Write (4)	0	0	Write Mask	1	Column Mask
Load Mask Data Register (2)	1	1	×	0	Write Mask Data
Load Color Register	1	1	×	1	Color Data

Note:

- (1) Reference truth table to determine the input signal states of *1, *2, *3, *4, and *5 for the write cycle timing diagram on the following pages
- (2) Old Mask data load
- (3) Function table for Old Mask and New Mask

IF		*1		*3	Note
		WBL/WEL	WBU/WEU	Wi/DQi	
LMR Cycle Executed	Yes	0	0	×	Write using mask register data (Old Mask Data)
		0	1	×	
		1	0	×	
	No	1	1	×	Non Masked Write
		0	0	Write Mask	Write using New Mask Data
		0	1	Mask	Wi/DQi=0 Write Disable
	1	0		Wi/DQi=1 Write Enable	
	1	1	×	Non Masked Write	

× : Don't Care

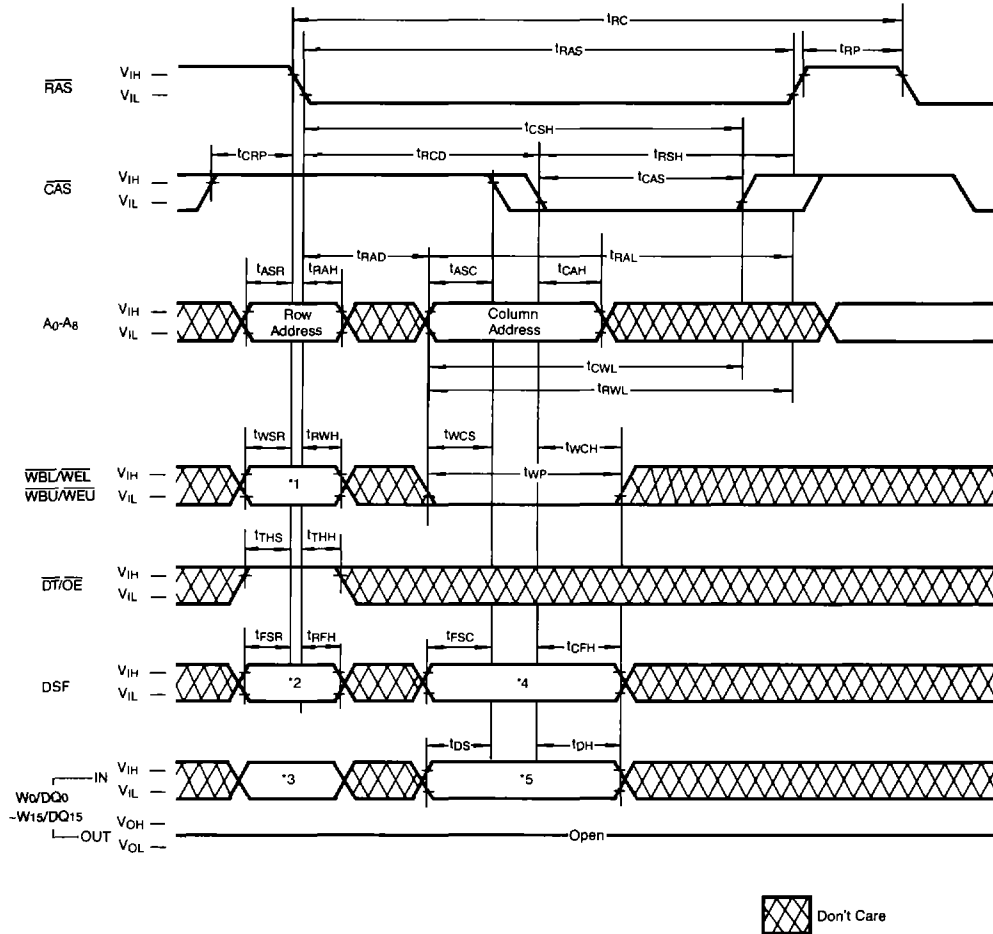
(4) Function Table for Block Write Column Mask

Column Address			*5		IF	
A2	A1	A0	Lower Byte	Upper Byte	Wi/DQi=0	Wi/DQi=1
0	0	0	W0/DQ0	W8/DQ8	No Change the Internal Data	Color Register Data are Write to the Corresponding Column Address Location
0	0	1	W1/DQ1	W9/DQ9		
0	1	0	W2/DQ2	W10/DQ10		
0	1	1	W3/DQ3	W11/DQ11		
1	0	0	W4/DQ4	W12/DQ12		
1	0	1	W5/DQ5	W13/DQ13		
1	1	0	W6/DQ6	W14/DQ14		
1	1	1	W7/DQ7	W15/DQ15		

PRELIMINARY
CMOS VIDEO RAM

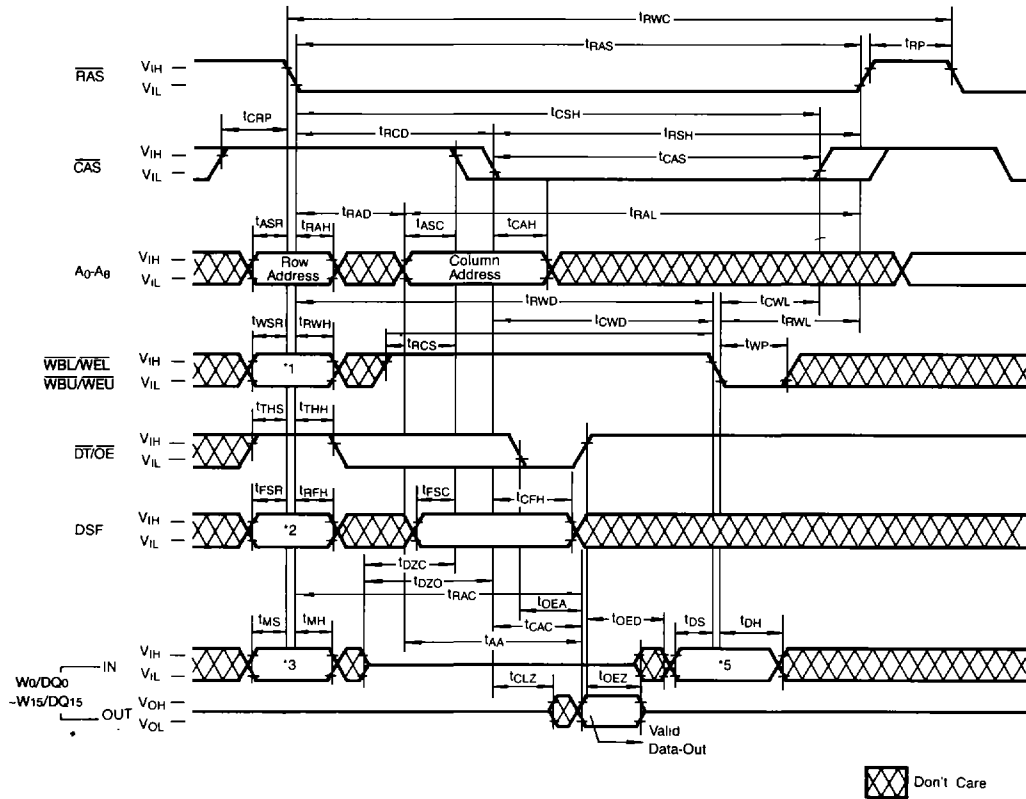
KM4216C256/L/F, KM4216V256/L/F

EARLY WRITE CYCLE



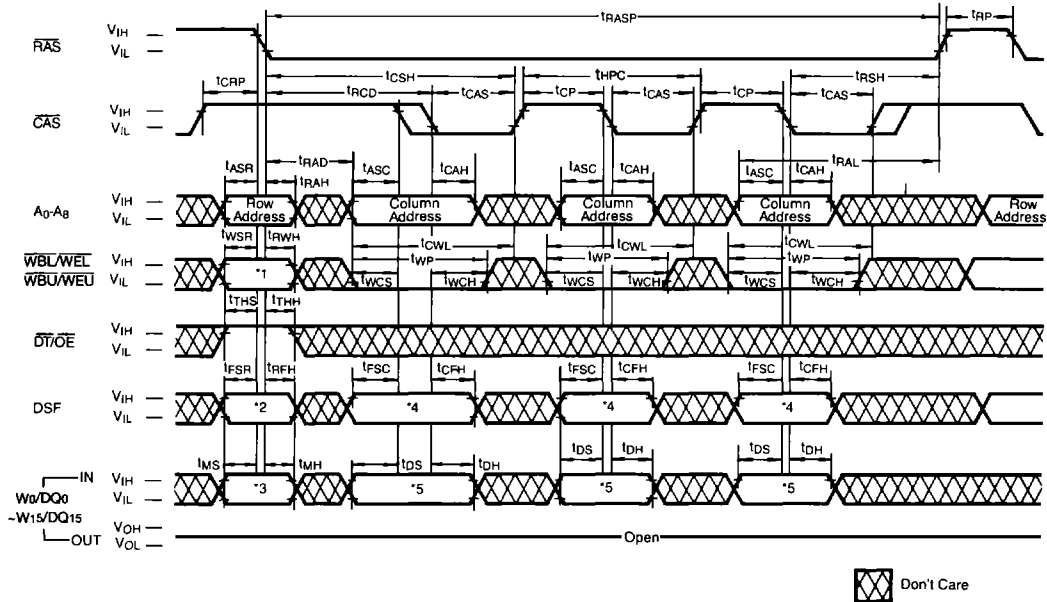
Note : In Block write cycle, only column address A₃~A₈ are used.

READ-WRITE/READ-MODIFY-WRITE CYCLE



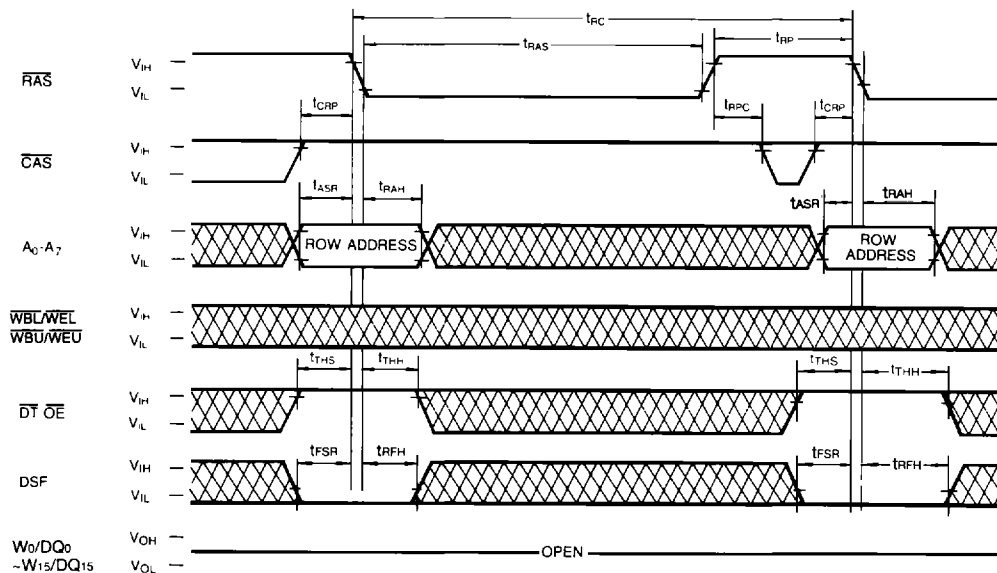
Note : In Block write cycle, only column address A3-A8 are used.

FAST PAGE MODE EARLY WRITE CYCLE



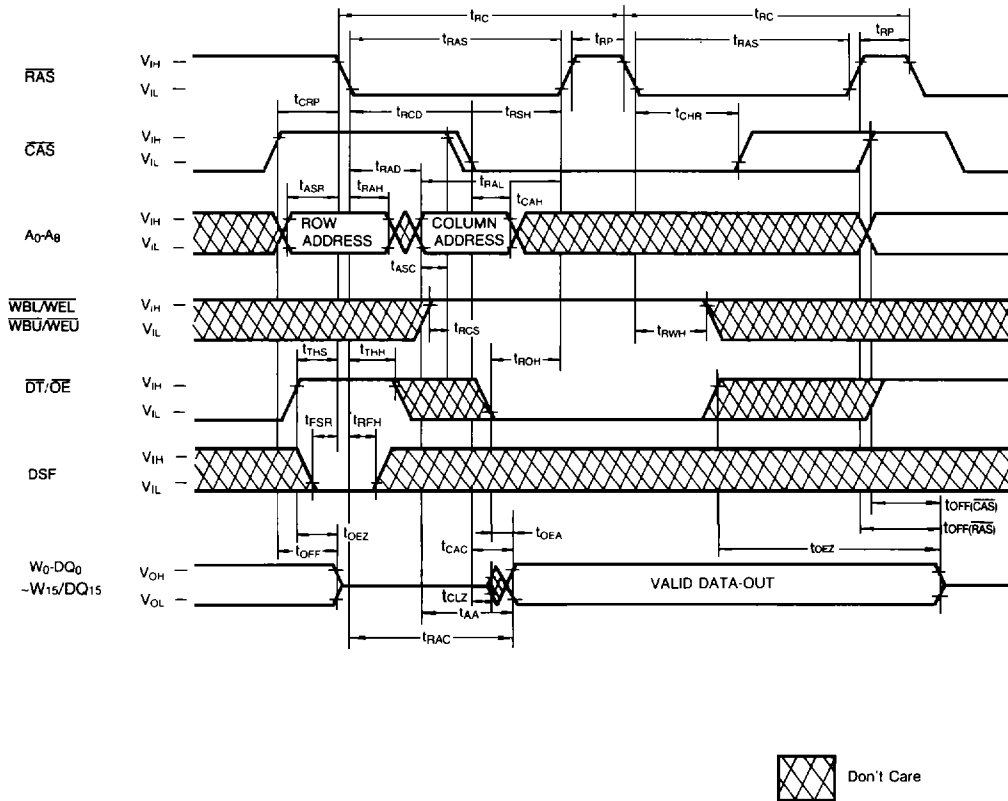
Note : In Block write cycle, only column address A3-A8 are used.

RAS ONLY REFRESH CYCLE

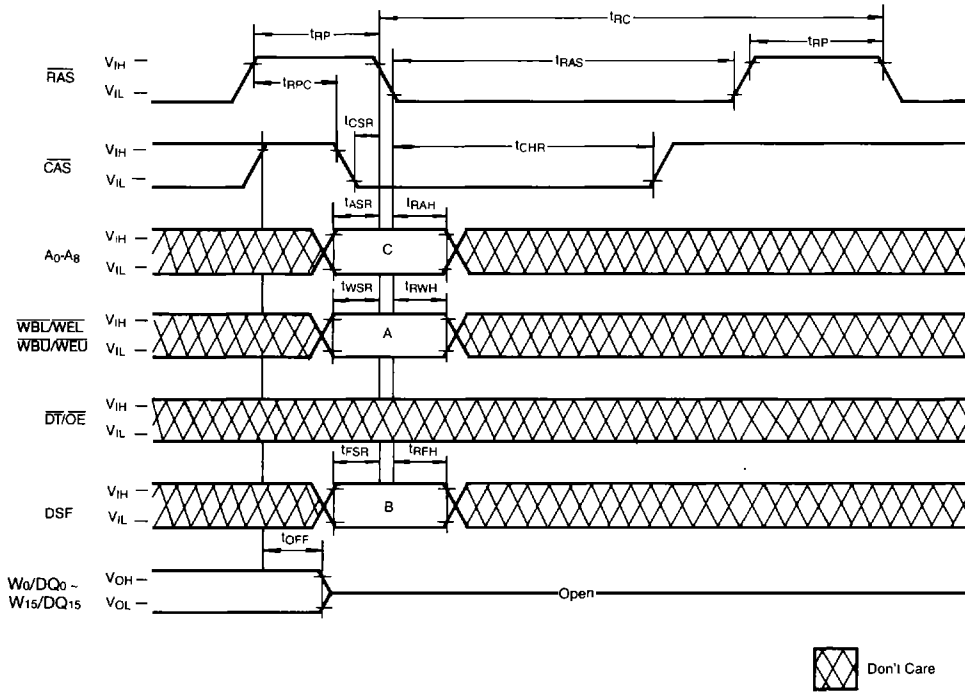


 DON'T CARE

HIDDEN REFRESH CYCLE



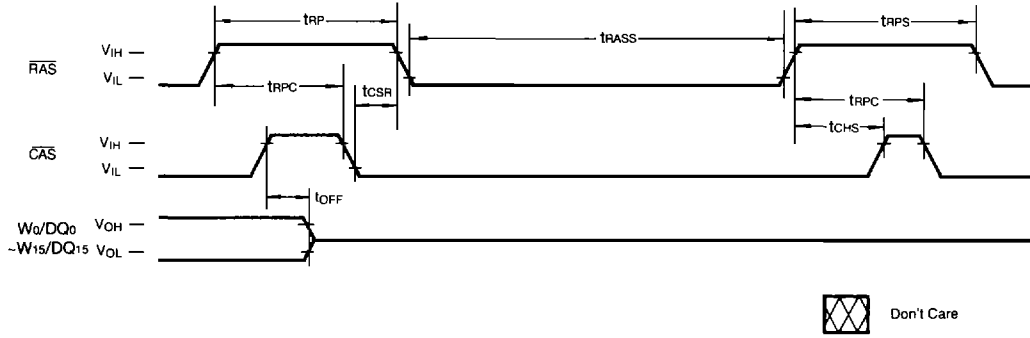
$\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ REFRESH CYCLE



$\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ REFRESH CYCLE FUNCTION TABLE

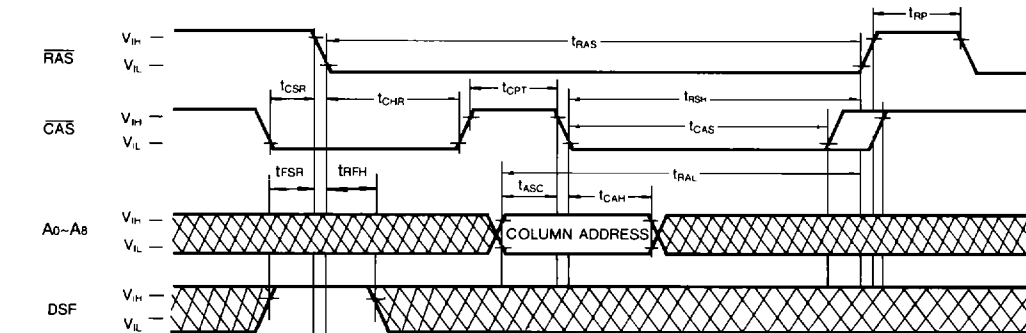
FUNCTION	CODE	LOGIC STATES		
		A	B	C
$\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ REFRESH CYCLE (Reset All Options)	CBRR	X	0	X
$\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ REFRESH CYCLE (Stop Register Set)	CBRS	0	1	STOP Address
$\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ REFRESH CYCLE (No Reset)	CBRN	1	1	X

CAS-BEFORE-RAS SELF REFRESH CYCLE

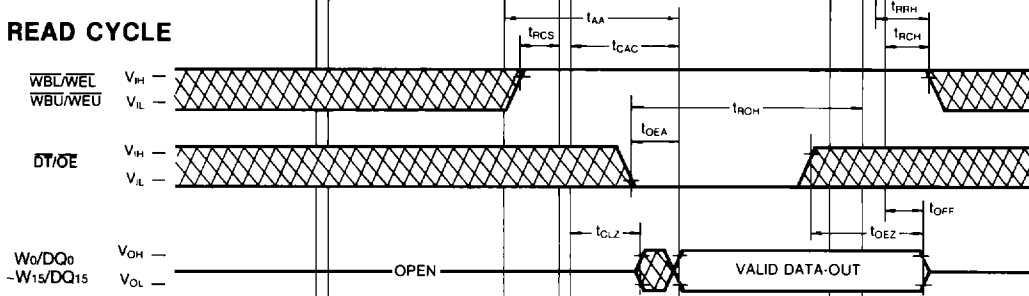


*CBR SELF REFRESH CYCLE IS APPLICABLE WITH CBRR, CBRS, OR CBRN CYCLE

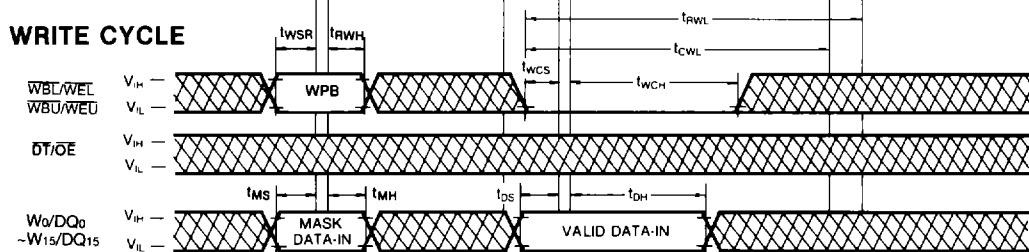
CAS-BEFORE-RAS REFRESH CYCLE TEST CYCLE



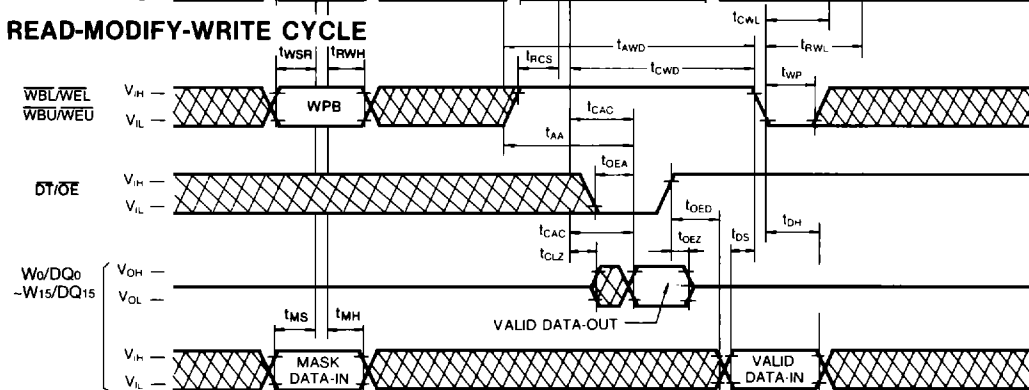
READ CYCLE



WRITE CYCLE

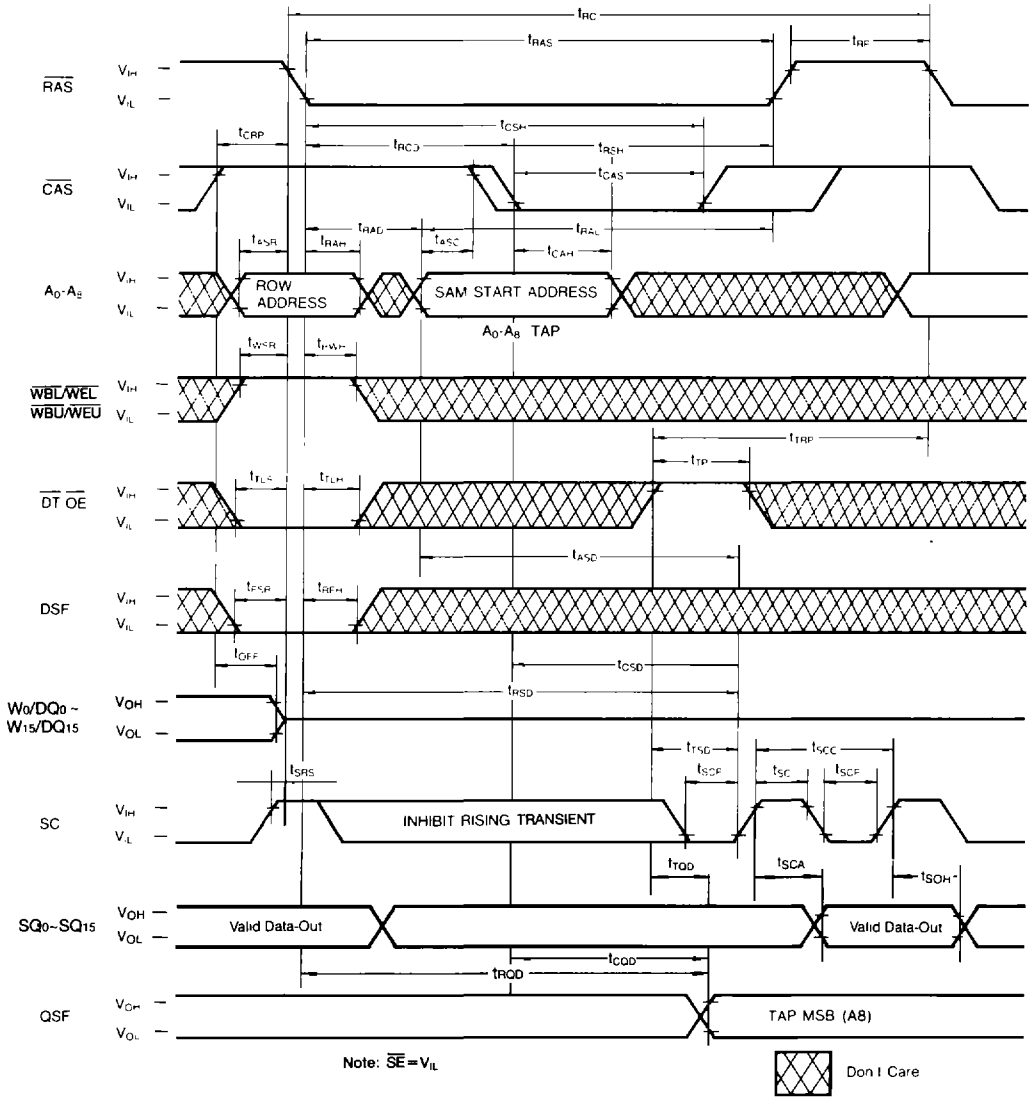


READ-MODIFY-WRITE CYCLE

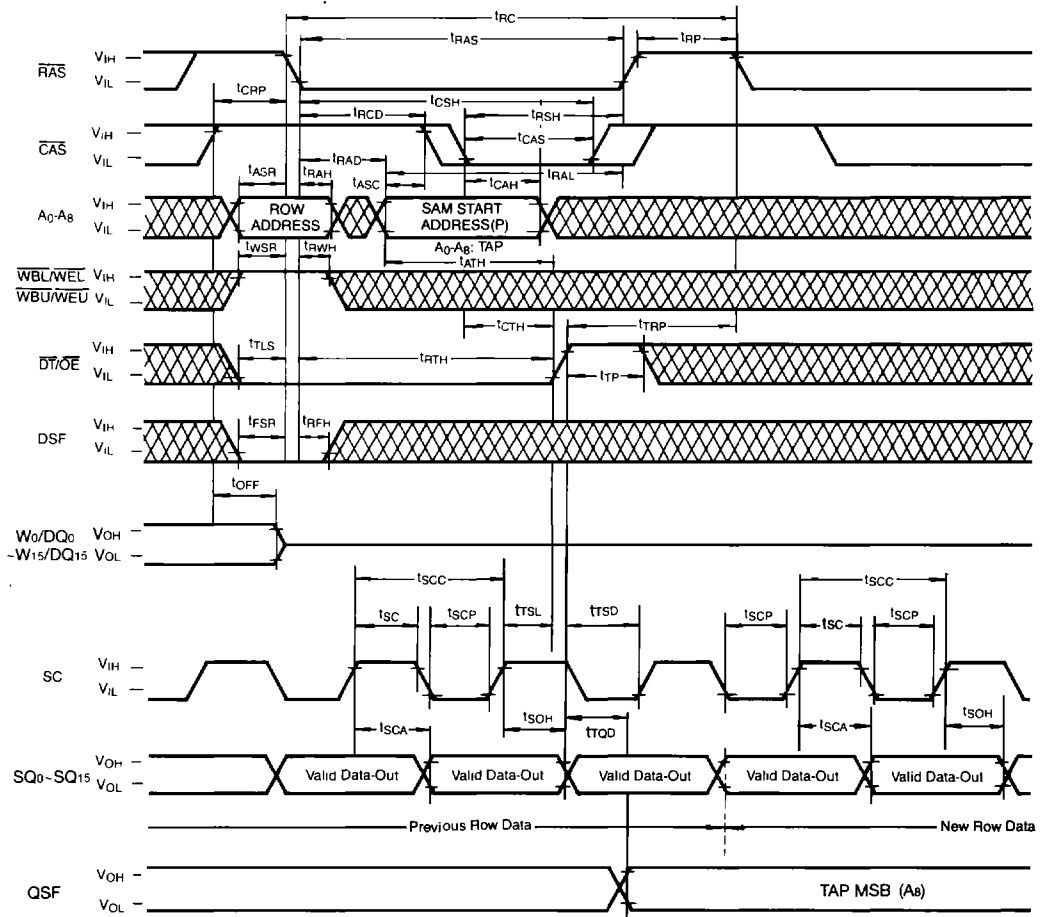


 DON'T CARE

READ TRANSFER CYCLE



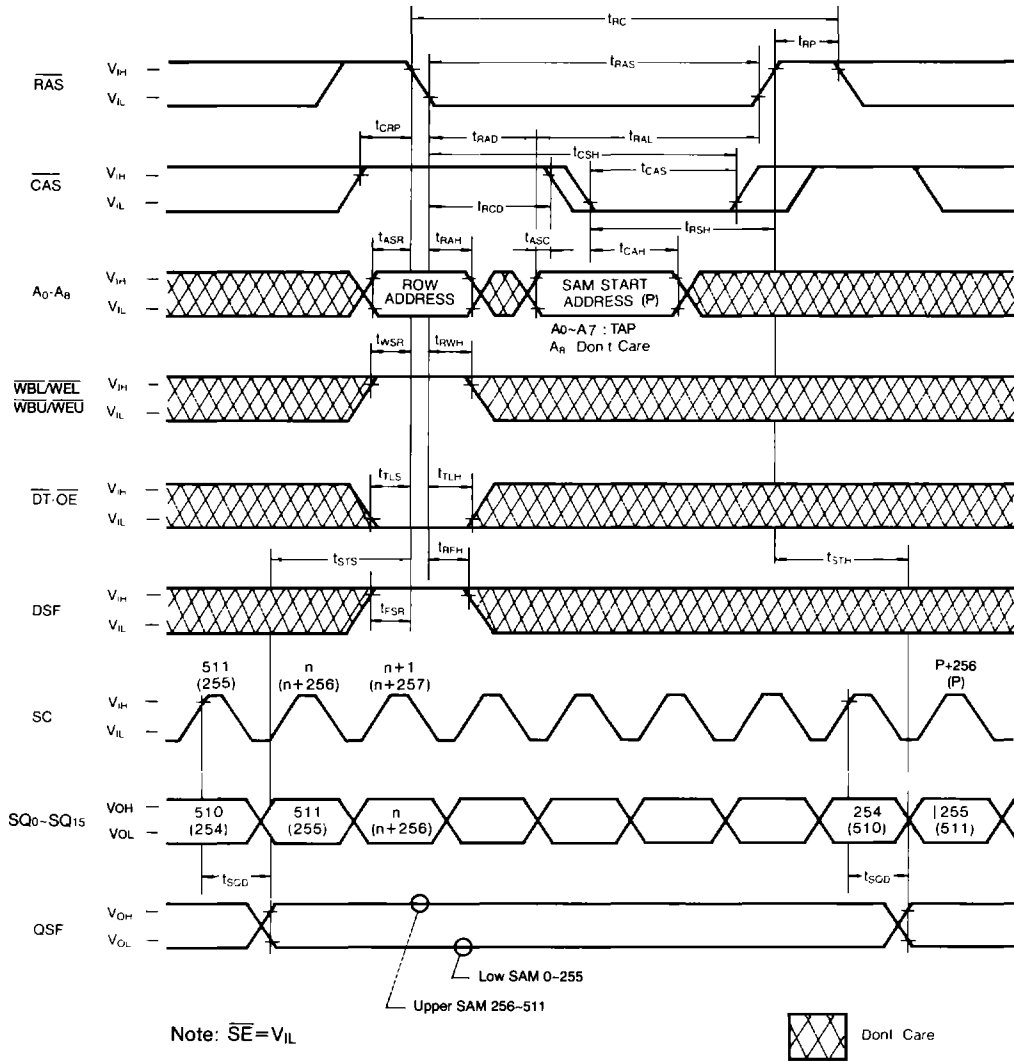
REAL TIME READ TRANSFER CYCLE



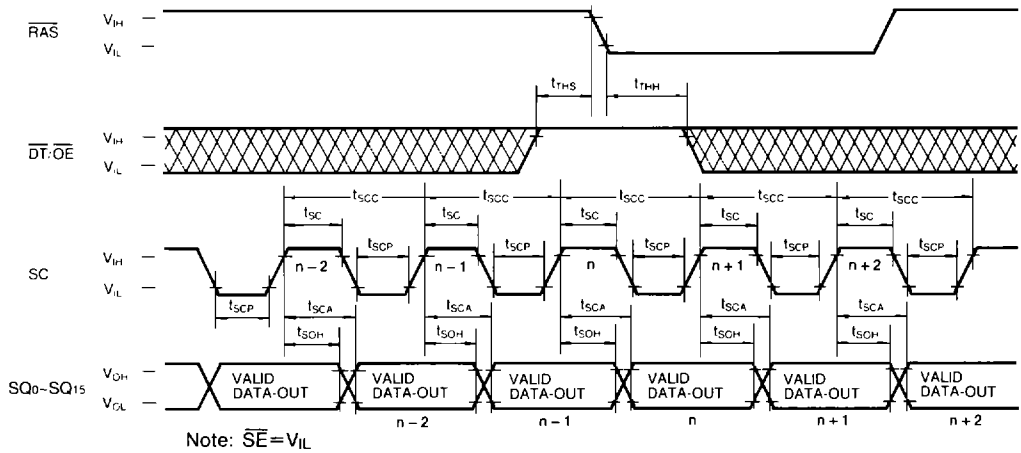
Note $\overline{SE} = V_{IL}$

 Don't Care

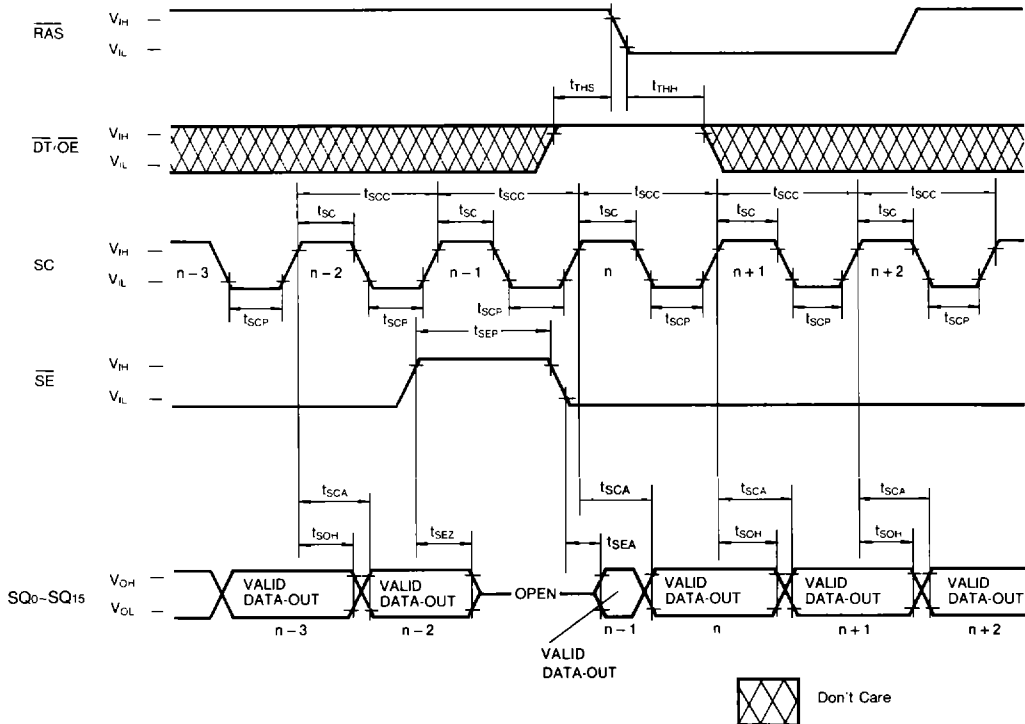
SPLIT READ TRANSFER CYCLE



SERIAL READ CYCLE ($\overline{SE} = V_{IL}$)



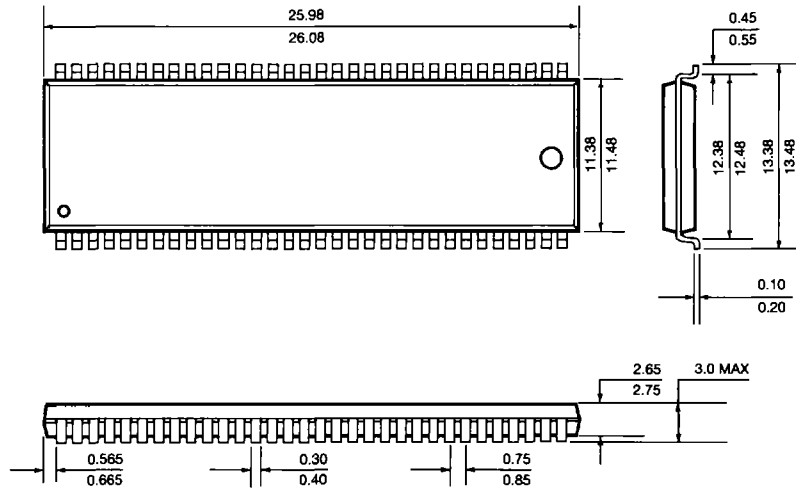
SERIAL READ CYCLE (\overline{SE} Controlled Outputs)



PACKAGE DIMENSIONS

64 Pin Plastic Shrink Small Out Line Package

Units: Millimeters



70(64) Pin Plastic Thin Small Out Line Package (Type II Forward)

